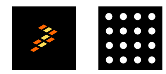
Kinetis K22F 128KB Flash 49-pin WLCSP: MK22FN128CAK10R

100 MHz Cortex-M4 Based Microcontroller with FPU

This K22 product family member is optimized for space-constrained, cost-sensitive applications requiring low-power, USB connectivity, and processing efficiency with a floating point unit. This device shares the comprehensive enablement and scalability of the Kinetis family.
This product offers:

- Run power consumption down to 120 μA/MHz and static power consumption down to 2.6 μA with full state retention and 6 μs wakeup. Lowest static mode down to 120 nA.
- USB LS/FS OTG 2.0 with embedded 3.3 V, 120 mA LDO voltage regulator. USB FS device crystal-less functionality.

MK22FN128CAK10



49 WLCSP (AK)
2.915 x 3.142 x 0.564 Pitch 0.4 mm

Performance
- 100 MHz ARM Cortex-M4 core with DSP instructions delivering 1.25 Dhrystone MIPS per MHz

Memories and memory interfaces
- 128 KB of embedded flash and 24 KB of RAM
- Serial programming interface (EzPort)
- Preprogrammed Kinetis flashloader for one-time, in-system factory programming

System peripherals
- Flexible low-power modes, multiple wake up sources
- 4-channel DMA controller
- Independent External and Software Watchdog monitor

Clocks
- Two crystal oscillators: 32 kHz (RTC) and 32-40 kHz or 3-32 MHz
- Three internal oscillators: 32 kHz, 4 MHz, and 48 MHz
- Multi-purpose clock generator with FLL

Security and integrity modules
- Hardware CRC module
- 128-bit unique identification (ID) number per chip
- Flash access control to protect proprietary software

Human-machine interface
- 35 general-purpose I/O (GPIO)

Analog modules
- Two 16-bit SAR ADCs (1.2 MS/s in 12bit mode)
- One 12-bit DAC (internal connection only)
- Two analog comparators (CMP) with 6-bit DAC
- Accurate internal voltage reference

Communication interfaces
- USB LS/FS OTG 2.0 with on-chip transceiver (Device mode only)
- USB full-speed device crystal-less operation
- Two SPI modules
- Three UART modules and one low-power UART
- Two I2C: Support for up to 1 Mbps operation with maximum bus loading
- I2S module

Timers
- One 8-channel general purpose PWM timer
- Two 2-channel general-purpose timers with quadrature decoder functionality
- Periodic interrupt timers
- 16-bit low-power timer
- Real-time clock with independent power domain
- Programmable delay block

Operating Characteristics
- Voltage range (including flash writes): 1.71 to 3.6 V
- Temperature range (ambient): -40 to 85°C

Ordering Information

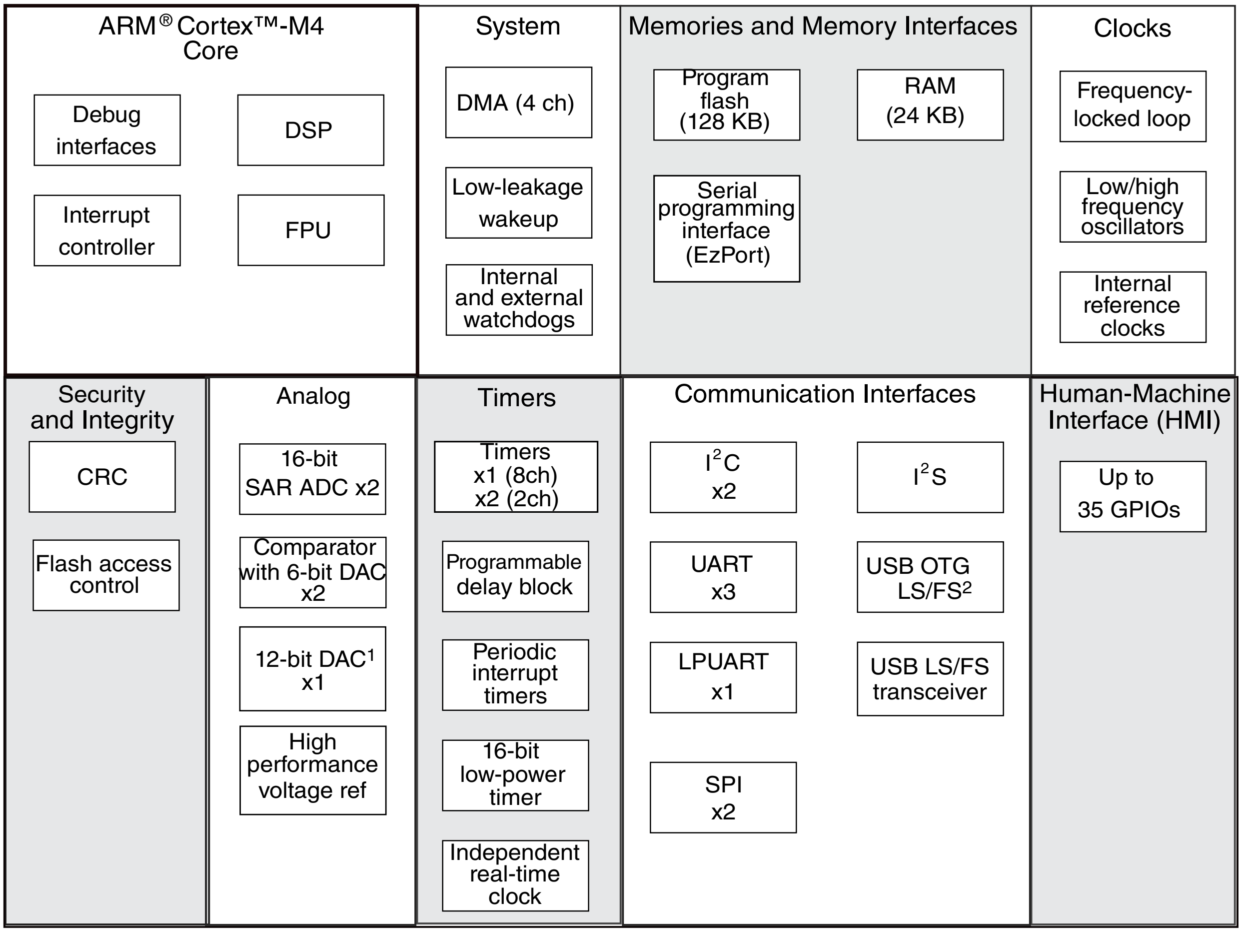
Part Number	Memory		Number of GPIOs
	Flash (KB)	SRAM (KB)	
MK22FN128CAK10R[1]	128	24	35

1. This package is not yet available; however, it is included in a Package Your Way program for Kinetis MCUs. Please visit www.Freescale.com/KPYW for more details.

Related Resources

Type	Description
Selector Guide	The Freescale Solution Advisor is a web-based tool that features interactive application wizards and a dynamic product selector.
Product Brief	The Product Brief contains concise overview/summary information to enable quick evaluation of a device for design suitability.
Reference Manual	The Reference Manual contains a comprehensive description of the structure and function (operation) of a device.
Data Sheet	The Data Sheet includes electrical characteristics and signal connections.
Chip Errata	The chip mask set Errata provides additional or corrective information for a particular device mask set.
Package drawing	Package dimensions are provided in package drawings.

Figure 1 shows the functional modules in the chip.



1. This device does not have the DAC0_OUT signal available; therefore, the DAC is only usable for internal connections.
2. This device does not have the USB_CLKIN signal available and therefore cannot support Host mode operation.

Figure 1. Functional block diagram

Table of Contents

1 Ratings.......5
1.1 Thermal handling ratings.......5
1.2 Moisture handling ratings.......5
1.3 ESD handling ratings.......5
1.4 Voltage and current operating ratings.......5
2 General.......6
2.1 AC electrical characteristics.......6
2.2 Nonswitching electrical specifications.......6
2.2.1 Voltage and current operating requirements.......6
2.2.2 LVD and POR operating requirements.......7
2.2.3 Voltage and current operating behaviors.......8
2.2.4 Power mode transition operating behaviors.......9
2.2.5 Power consumption operating behaviors.......10
2.2.6 EMC radiated emissions operating behaviors.......16
2.2.7 Designing with radiated emissions in mind.......17
2.2.8 Capacitance attributes.......17
2.3 Switching specifications.......17
2.3.1 Device clock specifications.......17
2.3.2 General switching specifications.......18
2.4 Thermal specifications.......19
2.4.1 Thermal operating requirements.......19
2.4.2 Thermal attributes.......19
3 Peripheral operating requirements and behaviors.......20
3.1 Core modules.......20
3.1.1 SWD electricals.......20
3.1.2 JTAG electricals.......21
3.2 System modules.......24
3.3 Clock modules.......24
3.3.1 MCG specifications.......24
3.3.2 IRC48M specifications.......26
3.3.3 Oscillator electrical specifications.......27
3.3.4 32 kHz oscillator electrical characteristics.......29
3.4 Memories and memory interfaces.......30
3.4.1 Flash electrical specifications.......30
3.4.2 EzPort switching specifications.......31
3.5 Security and integrity modules.......32
3.6 Analog.......32
3.6.1 ADC electrical specifications.......33
3.6.2 CMP and 6-bit DAC electrical specifications.......37
3.6.3 12-bit DAC electrical characteristics.......39
3.6.4 Voltage reference electrical specifications.......42
3.7 Timers.......43
3.8 Communication interfaces.......43
3.8.1 USB electrical specifications.......44
3.8.2 DSPI switching specifications (limited voltage range).......44
3.8.3 DSPI switching specifications (full voltage range).......46
3.8.4 Inter-Integrated Circuit Interface (I2C) timing.......47
3.8.5 UART switching specifications.......49
3.8.6 I2S/SAI switching specifications.......49
4 Dimensions.......55
4.1 Obtaining package dimensions.......55
5 Pinout.......56
5.1 K22 Signal Multiplexing and Pin Assignments.......56
5.2 K22 Pinouts.......58
6 Part identification.......59
6.1 Description.......59
6.2 Format.......59
6.3 Fields.......59
6.4 Example.......60
6.5 49-pin WLCSP part marking.......60
7 Revision History.......61

1 Ratings

1.1 Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
T_{STG}	Storage temperature	–55	150	°C	1
T_{SDR}	Solder temperature, lead-free	—	260	°C	2

1. Determined according to JEDEC Standard JESD22-A103, *High Temperature Storage Life*.
2. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

1.2 Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	—	1	—	1

1. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

1.3 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V_{HBM}	Electrostatic discharge voltage, human body model	-2000	+2000	V	1
V_{CDM}	Electrostatic discharge voltage, charged-device model	-500	+500	V	2
I_{LAT}	Latch-up current at ambient temperature of 105°C	-100	+100	mA	3

1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
2. Determined according to JEDEC Standard JESD22-C101, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components*.
3. Determined according to JEDEC Standard JESD78, *IC Latch-Up Test*.

1.4 Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
V_{DD}	Digital supply voltage	–0.3	3.8	V
I_{DD}	Digital supply current	—	145	mA
V_{DIO}	Digital input voltage	–0.3	V_{DD} + 0.3	V
V_{AIO}	Analog[1]	–0.3	V_{DD} + 0.3	V
I_D	Maximum current single pin limit (applies to all digital pins)	–25	25	mA
V_{DDA}	Analog supply voltage	V_{DD} – 0.3	V_{DD} + 0.3	V
V_{USB0_DP}	USB0_DP input voltage	–0.3	3.63	V
V_{USB0_DM}	USB0_DM input voltage	–0.3	3.63	V
V_{BAT}	RTC battery supply voltage	–0.3	3.8	V

1. Analog pins are defined as pins that do not have an associated general purpose I/O port function.

2 General

2.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.

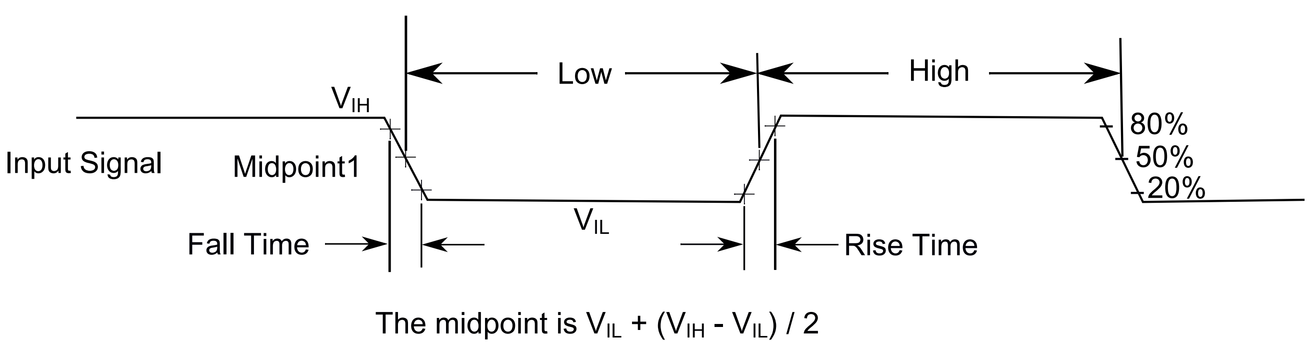


Figure 2. Input signal measurement reference

2.2 Nonswitching electrical specifications

2.2.1 Voltage and current operating requirements

Table 1. Voltage and current operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	3.6	V	
V_{DDA}	Analog supply voltage	1.71	3.6	V	
$V_{DD} – V_{DDA}$	V_{DD}-to-V_{DDA} differential voltage	–0.1	0.1	V	
$V_{SS} – V_{SSA}$	V_{SS}-to-V_{SSA} differential voltage	–0.1	0.1	V	
V_{BAT}	RTC battery supply voltage	1.71	3.6	V	
$USBV_{DD}$	USB Transceiver supply voltage	3.0	3.6	V	1
V_{IH}	Input high voltage • 2.7 V ≤ V_{DD} ≤ 3.6 V • 1.7 V ≤ V_{DD} ≤ 2.7 V	0.7 × V_{DD} 0.75 × V_{DD}	— —	V V	
V_{IL}	Input low voltage • 2.7 V ≤ V_{DD} ≤ 3.6 V • 1.7 V ≤ V_{DD} ≤ 2.7 V	— —	0.35 × V_{DD} 0.3 × V_{DD}	V V	
V_{HYS}	Input hysteresis	0.06 × V_{DD}	—	V	
I_{ICIO}	Analog and I/O pin DC injection current — single pin • V_{IN} < V_{SS}-0.3V (Negative current injection)	-3	—	mA	2
I_{ICcont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins • Negative current injection	-25	—	mA	
V_{ODPU}	Open drain pullup voltage level	V_{DD}	V_{DD}	V	3
V_{RAM}	V_{DD} voltage required to retain RAM	1.2	—	V	
V_{RFVBAT}	V_{BAT} voltage required to retain the VBAT register file	V_{POR_VBAT}	—	V	

1. USB nominal operating voltage is 3.3 V.
2. All analog and I/O pins are internally clamped to V_{SS} through ESD protection diodes. If V_{IN} is less than V_{IO_MIN} or greater than V_{IO_MAX}, a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{IO\_MIN}-V_{IN})/|I_{ICIO}|$.
3. Open drain outputs must be pulled to VDD.

2.2.2 LVD and POR operating requirements

Table 2. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR}	Falling VDD POR detect voltage	0.8	1.1	1.5	V	
V_{LVDH}	Falling low-voltage detect threshold — high range (LVDV=01)	2.48	2.56	2.64	V	

Table continues on the next page...

Table 2. V_{DD} supply LVD and POR operating requirements (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	Low-voltage warning thresholds — high range					1
V_{LVW1H}	• Level 1 falling (LVWV=00)	2.62	2.70	2.78	V	
V_{LVW2H}	• Level 2 falling (LVWV=01)	2.72	2.80	2.88	V	
V_{LVW3H}	• Level 3 falling (LVWV=10)	2.82	2.90	2.98	V	
V_{LVW4H}	• Level 4 falling (LVWV=11)	2.92	3.00	3.08	V	
V_{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	—	80	—	mV	
V_{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	
	Low-voltage warning thresholds — low range					1
V_{LVW1L}	• Level 1 falling (LVWV=00)	1.74	1.80	1.86	V	
V_{LVW2L}	• Level 2 falling (LVWV=01)	1.84	1.90	1.96	V	
V_{LVW3L}	• Level 3 falling (LVWV=10)	1.94	2.00	2.06	V	
V_{LVW4L}	• Level 4 falling (LVWV=11)	2.04	2.10	2.16	V	
V_{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	60	—	mV	
V_{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	
t_{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	μs	

1. Rising threshold is the sum of falling threshold and hysteresis voltage

Table 3. VBAT power operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR_VBAT}	Falling VBAT supply POR detect voltage	0.8	1.1	1.5	V	

2.2.3 Voltage and current operating behaviors

Table 4. Voltage and current operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{OH}	Output high voltage — Normal drive pad except RESET_B					
	$2.7\ V \le V_{DD} \le 3.6\ V$, $I_{OH} = -5\ mA$	$V_{DD} - 0.5$	—	—	V	1
	$1.71\ V \le V_{DD} \le 2.7\ V$, $I_{OH} = -2.5\ mA$	$V_{DD} - 0.5$	—	—	V	
V_{OH}	Output high voltage — High drive pad except RESET_B					
	$2.7\ V \le V_{DD} \le 3.6\ V$, $I_{OH} = -20\ mA$	$V_{DD} - 0.5$	—	—	V	1

Table continues on the next page...

Table 4. Voltage and current operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = -10 mA	V_{DD} – 0.5	—	—	V	
I_{OHT}	Output high current total for all ports	—	—	100	mA	
V_{OL}	Output low voltage — Normal drive pad except RESET_B					
	2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 5 mA	—	—	0.5	V	1
	1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 2.5 mA	—	—	0.5	V	
V_{OL}	Output low voltage — High drive pad except RESET_B					
	2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 20 mA	—	—	0.5	V	1
	1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 10 mA	—	—	0.5	V	
V_{OL}	Output low voltage — RESET_B					
	2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 3 mA	—	—	0.5	V	
	1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 1.5 mA	—	—	0.5	V	
I_{OLT}	Output low current total for all ports	—	—	100	mA	
I_{IN}	Input leakage current (per pin) for full temperature range					
	All pins other than high drive port pins	—	0.002	0.5	μA	1, 2
	High drive port pins	—	0.004	0.5	μA	
I_{IN}	Input leakage current (total all pins) for full temperature range	—	—	1.0	μA	2
R_{PU}	Internal pullup resistors	20	—	50	kΩ	3
R_{PD}	Internal pulldown resistors	20	—	50	kΩ	4

1. PTB0, PTB1, PTC3, PTC4, PTD4, PTD5, PTD6, and PTD7 I/O have both high drive and normal drive capability selected by the associated PTx_PCRn[DSE] control bit. All other GPIOs are normal drive only.
2. Measured at VDD=3.6V
3. Measured at V_{DD} supply voltage = V_{DD} min and Vinput = V_{SS}
4. Measured at V_{DD} supply voltage = V_{DD} min and Vinput = V_{DD}

2.2.4 Power mode transition operating behaviors

All specifications except t_{POR}, and VLLSx→RUN recovery times in the following table assume this clock configuration:

- CPU and system clocks = 72 MHz
- Bus clock = 36 MHz
- Flash clock = 24 MHz
- MCG mode: FEI

Table 5. Power mode transition operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{POR}	After a POR event, amount of time from the point V_{DD} reaches 1.71 V to execution of the first instruction across the operating temperature range of the chip.	—	—	300	μs	1
	• VLLS0 → RUN	—	—	135	μs	
	• VLLS1 → RUN	—	—	135	μs	
	• VLLS2 → RUN	—	—	75	μs	
	• VLLS3 → RUN	—	—	75	μs	
	• LLS2 → RUN	—	—	6	μs	
	• LLS3 → RUN	—	—	6	μs	
	• VLPS → RUN	—	—	5.7	μs	
	• STOP → RUN	—	—	5.7	μs	

1. Normal boot (FTFA_OPT[LPBOOT]=1)

2.2.5 Power consumption operating behaviors

The current parameters in the table below are derived from code executing a while(1) loop from flash, unless otherwise noted.

The IDD typical values represent the statistical mean at 25°C, and the IDD maximum values for RUN, WAIT, VLPR, and VLPW represent data collected at 125°C junction temperature unless otherwise noted. The maximum values represent characterized results equivalent to the mean plus three times the standard deviation (mean + 3 sigma).

Table 6. Power consumption operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA}	Analog supply current	—	—	See note	mA	1
I_{DD_HSRUN}	High Speed Run mode current - all peripheral clocks disabled, CoreMark benchmark code executing from flash					

Table continues on the next page...

Table 6. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	@ 1.8V	—	19.51	20.24	mA	2, 3, 4
	@ 3.0V	—	19.51	20.24	mA	
I_{DD_HSRUN}	High Speed Run mode current - all peripheral clocks disabled, code executing from flash					
	@ 1.8V	—	16.9	17.63	mA	5
	@ 3.0V	—	17.0	17.73	mA	
I_{DD_HSRUN}	High Speed Run mode current — all peripheral clocks enabled, code executing from flash					
	@ 1.8V	—	22.8	23.53	mA	6
	@ 3.0V	—	22.9	23.63	mA	
I_{DD_RUN}	Run mode current in Compute operation — CoreMark benchmark code executing from flash					
	@ 1.8V	—	11.39	12.12	mA	2, 3, 7
	@ 3.0V	—	11.58	12.31	mA	
I_{DD_RUN}	Run mode current in Compute operation — code executing from flash					
	@ 1.8V	—	10.90	11.90	mA	7
	@ 3.0V	—	10.90	12.23	mA	
I_{DD_RUN}	Run mode current — all peripheral clocks disabled, code executing from flash					
	@ 1.8V	—	11.8	12.53	mA	8
	@ 3.0V	—	11.9	12.63	mA	
I_{DD_RUN}	Run mode current — all peripheral clocks enabled, code executing from flash					
	@ 1.8V	—	15.5	16.23	mA	9
	@ 3.0V					
	• @ 25°C	—	15.6	16.33	mA	
	• @ 70°C	—	15.6	16.33	mA	
	• @ 85°C	—	15.6	16.33	mA	
I_{DD_RUN}	Run mode current — Compute operation, code executing from flash					
	@ 1.8V	—	10.9	11.63	mA	10
	@ 3.0V					
	• @ 25°C	—	10.9	11.63	mA	
	• @ 70°C	—	10.9	11.63	mA	
	• @ 85°C	—	10.9	11.63	mA	
I_{DD_WAIT}	Wait mode high frequency current at 3.0 V — all peripheral clocks disabled	—	6.5	7.23	mA	8

Table continues on the next page...

Table 6. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DD_WAIT}	Wait mode reduced frequency current at 3.0 V — all peripheral clocks disabled	—	3.9	4.63	mA	11
I_{DD_VLPR}	Very-low-power run mode current in Compute operation — CoreMark benchmark code executing from flash					
	@ 1.8V	—	0.60	0.88	mA	2, 3, 12
	@ 3.0V	—	0.61	0.89	mA	
I_{DD_VLPR}	Very-low-power run mode current in Compute operation, code executing from flash					
	@ 1.8V	—	0.48	0.76	mA	12
	@ 3.0V	—	0.48	0.76	mA	
I_{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks disabled	—	0.54	0.82	mA	13
I_{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks enabled	—	0.79	1.07	mA	14
I_{DD_VLPW}	Very-low-power wait mode current at 3.0 V — all peripheral clocks disabled	—	0.30	0.59	mA	15
I_{DD_STOP}	Stop mode current at 3.0 V					
	@ -40°C to 25°C	—	0.27	0.33	mA	
	@ 70°C	—	0.31	0.36	mA	
	@ 85°C	—	0.31	0.36	mA	
I_{DD_VLPS}	Very-low-power stop mode current at 3.0 V					
	@ -40°C to 25°C	—	4.2	9.00	μA	
	@ 70°C	—	15.8	31.90	μA	
	@ 85°C	—	26.9	50.95	μA	
I_{DD_LLS3}	Low leakage stop mode 3 current at 3.0 V					
	@ -40°C to 25°C	—	2.6	3.30	μA	
	@ 70°C	—	6.2	8.60	μA	
	@ 85°C	—	9.6	12.30	μA	
I_{DD_LLS2}	Low leakage stop mode 2 current at 3.0 V					
	@ -40°C to 25°C	—	2.4	3.00	μA	
	@ 70°C	—	5.2	6.85	μA	
	@ 85°C	—	7.9	9.95	μA	
I_{DD_VLLS3}	Very low-leakage stop mode 3 current at 3.0 V					
	@ -40°C to 25°C	—	1.8	2.10	μA	
	@ 70°C	—	4.3	5.70	μA	
	@ 85°C	—	6.6	8.10	μA	
I_{DD_VLLS2}	Very low-leakage stop mode 2 current at 3.0 V					
	@ -40°C to 25°C	—	1.6	1.80	μA	
	@ 70°C	—	3.1	3.90	μA	
	@ 85°C	—	4.7	7.00	μA	

Table continues on the next page...

Table 6. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DD_VLLS1}	Very low-leakage stop mode 1 current at 3.0 V					
	@ -40°C to 25°C	—	0.70	0.90	μA	
	@ 70°C	—	1.78	2.09	μA	
	@ 85°C	—	2.8	3.25	μA	
I_{DD_VLLS0}	Very low-leakage stop mode 0 current at 3.0 V with POR detect circuit enabled					
	@ -40°C to 25°C	—	0.40	0.49	μA	
	@ 70°C	—	1.38	1.49	μA	
	@ 85°C	—	2.40	2.70	μA	
I_{DD_VLLS0}	Very low-leakage stop mode 0 current at 3.0 V with POR detect circuit disabled					
	@ -40°C to 25°C	—	0.12	0.19	μA	
	@ 70°C	—	1.05	1.13	μA	
	@ 85°C	—	2.1	2.45	μA	
I_{DD_VBAT}	Average current with RTC and 32kHz disabled at 3.0 V					
	@ -40°C to 25°C	—	0.18	0.21	μA	
	@ 70°C	—	0.66	0.86	μA	
	@ 85°C	—	1.52	2.24	μA	
I_{DD_VBAT}	Average current when CPU is not accessing RTC registers					
	@ 1.8V					
	• @ -40°C to 25°C	—	0.57	0.67	μA	16
	• @ 70°C	—	0.90	1.2	μA	
	• @ 85°C	—	0.90	1.2	μA	
	@ 3.0V					
	• @ -40°C to 25°C	—	0.67	0.94	μA	
	• @ 70°C	—	1.0	1.4	μA	
	• @ 85°C	—	1.0	1.4	μA	

1. The analog supply current is the sum of the active or disabled current for each of the analog modules on the device. See each module's specification for its supply current.
2. Cache on and prefetch on, low compiler optimization.
3. Coremark benchmark compiled using IAR 7.2 withs optimization level low.
4. 100 MHz core and system clock, 50 MHz bus clock, and 25 MHz flash clock. MCG configured for FEE mode. All peripheral clocks disabled.
5. 100MHz core and system clock, 50MHz bus clock, and 25MHz flash clock. MCG configured for FEI mode. All peripheral clocks disabled.
6. 100MHz core and system clock, 50MHz bus clock, and 25MHz flash clock. MCG configured for FEI mode. All peripheral clocks enabled.
7. 72 MHz core and system clock, 36 MHz bus clock, and 24 MHz flash clock. MCG configured for FEE mode. All peripheral clocks disabled. Compute operation.

8. 72MHz core and system clock, 36MHz bus clock, and 24MHz flash clock. MCG configured for FEI mode. All peripheral clocks disabled.
9. 72MHz core and system clock, 36MHz bus clock, and 24MHz flash clock. MCG configured for FEI mode. All peripheral clocks enabled.
10. 72MHz core and system clock, 36MHz bus clock, and 24MHz flash clock. MCG configured for FEI mode. Compute Operation.
11. 25MHz core and system clock, 25MHz bus clock, and 25MHz flash clock. MCG configured for FEI mode.
12. 4 MHz core, system, and bus clock and 1MHz flash clock. MCG configured for BLPE mode. Compute Operation. Code executing from flash.
13. 4 MHz core, system, and bus clock and 1MHz flash clock. MCG configured for BLPE mode. All peripheral clocks disabled. Code executing from flash.
14. 4 MHz core, system, and bus clock and 1MHz flash clock. MCG configured for BLPE mode. All peripheral clocks enabled but peripherals are not in active operation. Code executing from flash.
15. 4 MHz core, system, and bus clock and 1MHz flash clock. MCG configured for BLPE mode. All peripheral clocks disabled.
16. Includes 32kHz oscillator current and RTC operation.

2.2.5.1 Diagram: Typical IDD_RUN operating behavior

The following data was measured under these conditions:

- MCG in FBE mode for 50 MHz and lower frequencies. MCG in FEE mode at frequencies between 50 MHz and 100MHz.
- No GPIOs toggled
- Code execution from flash with cache enabled
- For the ALLOFF curve, all peripheral clocks are disabled except FTFA

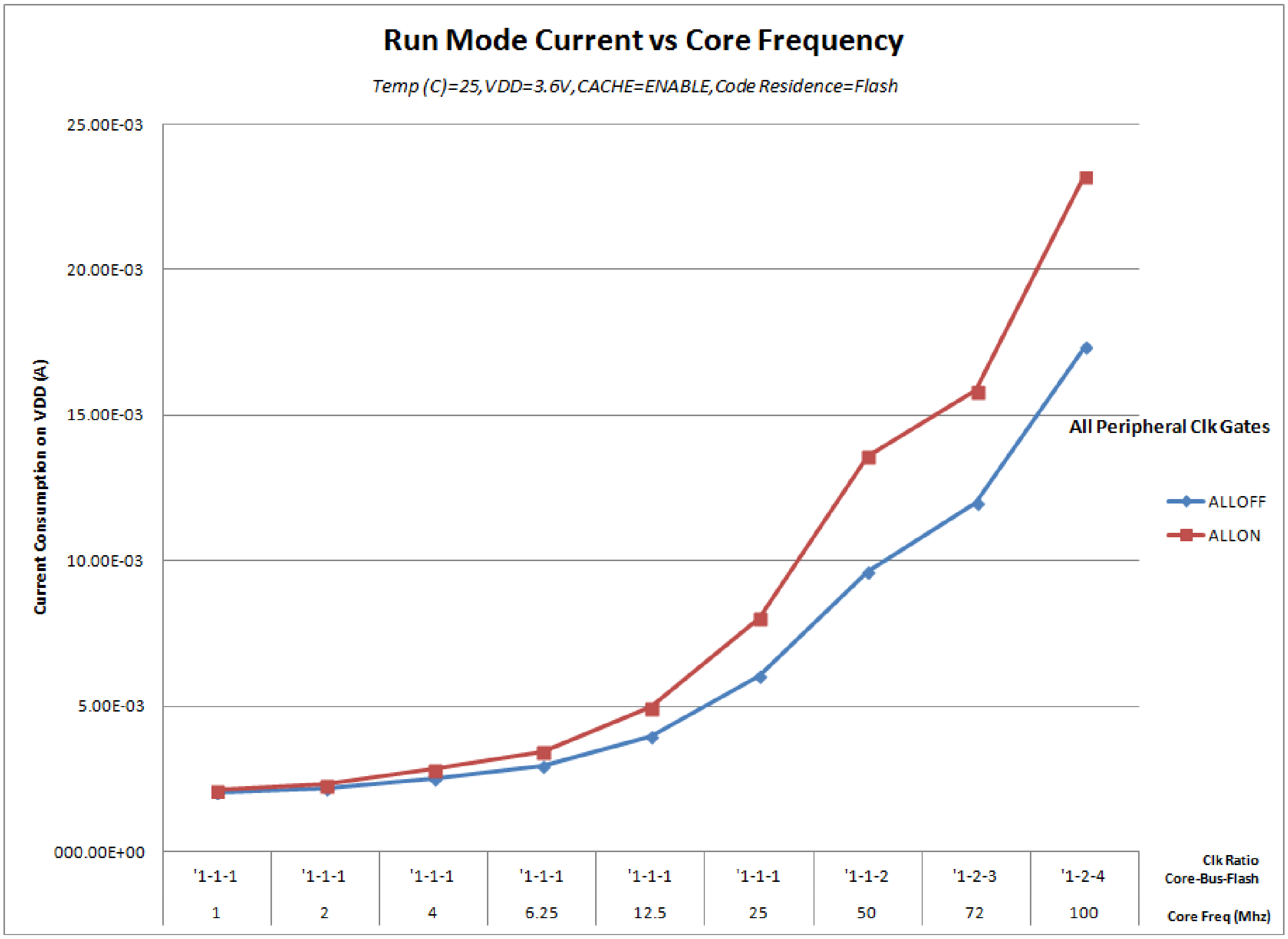


Figure 3. Run mode supply current vs. core frequency

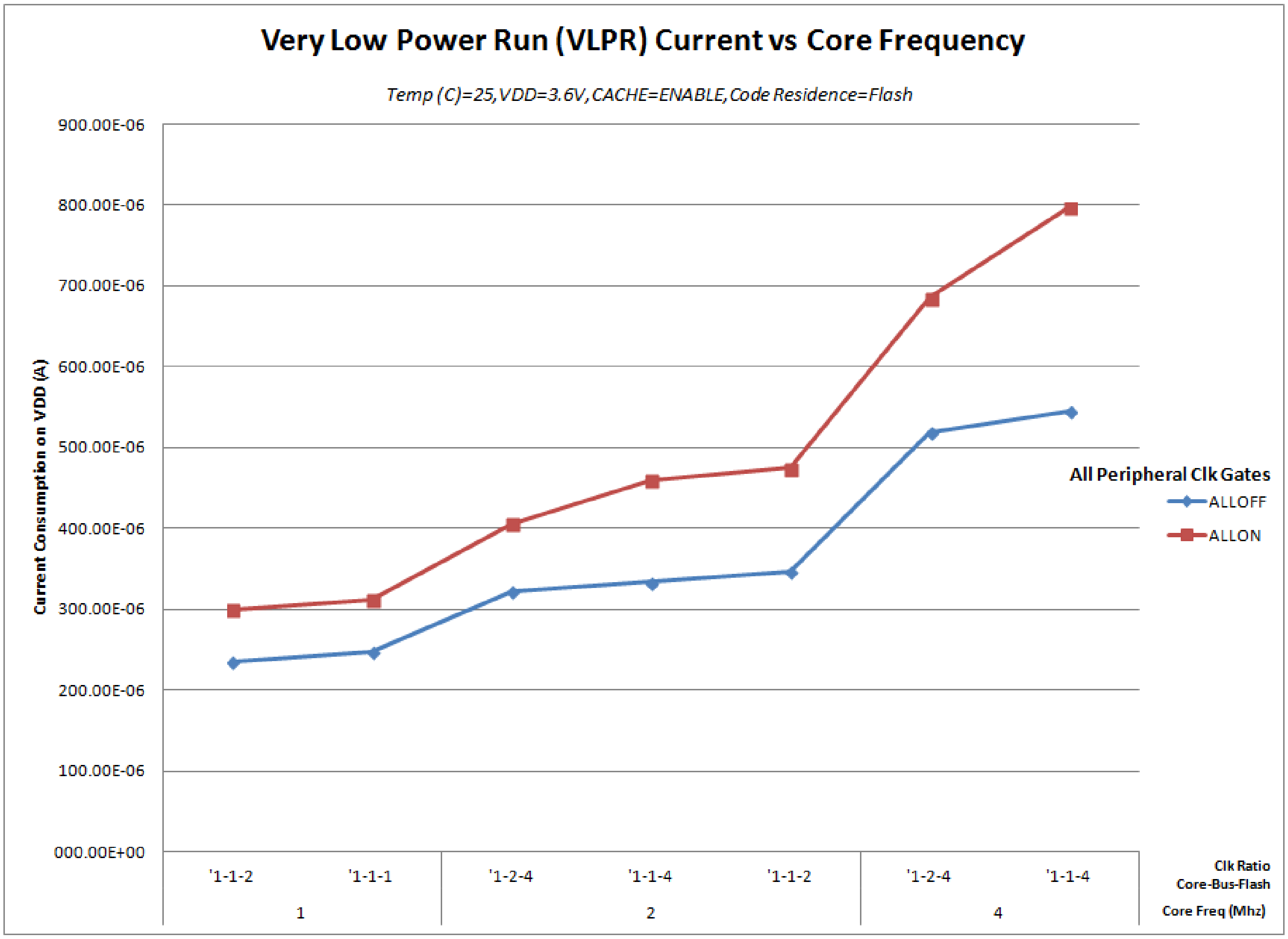


Figure 4. VLPR mode supply current vs. core frequency

2.2.6 EMC radiated emissions operating behaviors

Table 7. EMC radiated emissions operating behaviors for 64 LQFP package

Parameter	Conditions	Clocks	Frequency range	Level (Typ.)	Unit	Notes
V_{EME}	Device configuration, test conditions and EM testing per standard IEC 61967-2. Supply voltages: Temp = 25°C	FSYS = 100 MHz FBUS = 50 MHz External crystal = 10 MHz	150 kHz–50 MHz	13	dBuV	1, 2, 3
			50 MHz–150 MHz	24		
			150 MHz–500 MHz	23		
			500 MHz–1000 MHz	7		
			IEC level	L		4

1. Measurements were made per IEC 61967-2 while the device was running typical application code.
2. Measurements were performed on the 64LQFP device, MK22FN128VLH10 .
3. The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.
4. IEC Level Maximums: M ≤ 18dBmV, L ≤ 24dBmV, K ≤ 30dBmV, I ≤ 36dBmV, H ≤ 42dBmV .

2.2.7 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

1. Go to www.freescale.com.
2. Perform a keyword search for "EMC design."

2.2.8 Capacitance attributes

Table 8. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C_{IN_A}	Input capacitance: analog pins	—	7	pF
C_{IN_D}	Input capacitance: digital pins	—	7	pF

2.3 Switching specifications

2.3.1 Device clock specifications

Table 9. Device clock specifications

Symbol	Description	Min.	Max.	Unit	Notes
High Speed run mode					
f_{SYS}	System and core clock	—	100	MHz	
f_{BUS}	Bus clock	—	50	MHz	
Normal run mode (and High Speed run mode unless otherwise specified above)					
f_{SYS}	System and core clock	—	72	MHz	
f_{SYS_USB}	System and core clock when Full Speed USB in operation	20	—	MHz	
f_{BUS}	Bus clock	—	50	MHz	
f_{FLASH}	Flash clock	—	25	MHz	
f_{LPTMR}	LPTMR clock	—	25	MHz	
VLPR mode[1]					
f_{SYS}	System and core clock	—	4	MHz	
f_{BUS}	Bus clock	—	4	MHz	
f_{FLASH}	Flash clock	—	1	MHz	
f_{ERCLK}	External reference clock	—	16	MHz	

Table continues on the next page...

Table 9. Device clock specifications (continued)

Symbol	Description	Min.	Max.	Unit	Notes
f_{LPTMR_pin}	LPTMR clock	—	25	MHz	
f_{LPTMR_ERCLK}	LPTMR external reference clock	—	16	MHz	
f_{I2S_MCLK}	I2S master clock	—	12.5	MHz	
f_{I2S_BCLK}	I2S bit clock	—	4	MHz	

1. The frequency limitations in VLPR mode here override any frequency specification listed in the timing specification for any other module.

2.3.2 General switching specifications

These general purpose specifications apply to all signals configured for GPIO, UART, and timers.

Table 10. General switching specifications

Symbol	Description	Min.	Max.	Unit	Notes
	GPIO pin interrupt pulse width (digital glitch filter disabled) — Synchronous path	1.5	—	Bus clock cycles	1, 2
	External RESET and NMI pin interrupt pulse width — Asynchronous path	100	—	ns	3
	GPIO pin interrupt pulse width (digital glitch filter disabled, passive filter disabled) — Asynchronous path	50	—	ns	4
	Mode select ($\overline{EZP\_CS}$) hold time after reset deassertion	2	—	Bus clock cycles	
	Port rise and fall time				5
	• Slew disabled	—			
	• $1.71 \leq V_{DD} \leq 2.7V$	—	10	ns	
	• $2.7 \leq V_{DD} \leq 3.6V$		5	ns	
	• Slew enabled	—			
	• $1.71 \leq V_{DD} \leq 2.7V$	—	30	ns	
	• $2.7 \leq V_{DD} \leq 3.6V$		16	ns	

1. This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In Stop, VLPS, LLS, and VLLSx modes, the synchronizer is bypassed so shorter pulses can be recognized in that case.
2. The greater of synchronous and asynchronous timing must be met.
3. These pins have a passive filter enabled on the inputs. This is the shortest pulse width that is guaranteed to be recognized.
4. These pins do not have a passive filter on the inputs. This is the shortest pulse width that is guaranteed to be recognized.
5. 25 pF load

2.4 Thermal specifications

2.4.1 Thermal operating requirements

Table 11. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
T_J	Die junction temperature	–40	95	°C	
T_A	Ambient temperature	–40	85	°C	1

1. Maximum T_A can be exceeded only if the user ensures that T_J does not exceed maximum T_J. The simplest method to determine T_J is: $T_J = T_A + \Theta_{JA}$ X chip power dissipation.

2.4.2 Thermal attributes

Board type	Symbol	Description	49 WLCSP	Unit	Notes
Single-layer (1s)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	TBD	°C/W	1
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	45.3	°C/W	2
Single-layer (1s)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./ min. air speed)	TBD	°C/W	3
Four-layer (2s2p)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./ min. air speed)	TBD	°C/W	3
—	$R_{\theta JB}$	Thermal resistance, junction to board	35	°C/W	4
—	$R_{\theta JC}$	Thermal resistance, junction to case	TBD	°C/W	5
—	Ψ_{JT}	Thermal characterization	TBD	°C/W	6

Board type	Symbol	Description	49 WLCSP	Unit	Notes
		parameter, junction to package top outside center (natural convection)			

1. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)*with the single layer board horizontal. Board meets JESD51-9 specification.
2. Determined according to JEDEC Standard JESD51-2, Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air).
3. Determined according to JEDEC Standard JESD51-6, Integrated Circuits Thermal Test Method Environmental Conditions—Forced Convection (Moving Air) with the board horizontal.
4. Determined according to JEDEC Standard JESD51-8, *Integrated Circuit Thermal Test Method Environmental Conditions—Junction-to-Board*.
5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2.

3 Peripheral operating requirements and behaviors

3.1 Core modules

3.1.1 SWD electricals

Table 12. SWD full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	SWD_CLK frequency of operation • Serial wire debug	0	33	MHz
S2	SWD_CLK cycle period	1/S1	—	ns
S3	SWD_CLK clock pulse width • Serial wire debug	15	—	ns
S4	SWD_CLK rise and fall times	—	3	ns
S9	SWD_DIO input data setup time to SWD_CLK rise	8	—	ns
S10	SWD_DIO input data hold time after SWD_CLK rise	1.4	—	ns
S11	SWD_CLK high to SWD_DIO data valid	—	25	ns
S12	SWD_CLK high to SWD_DIO high-Z	5	—	ns

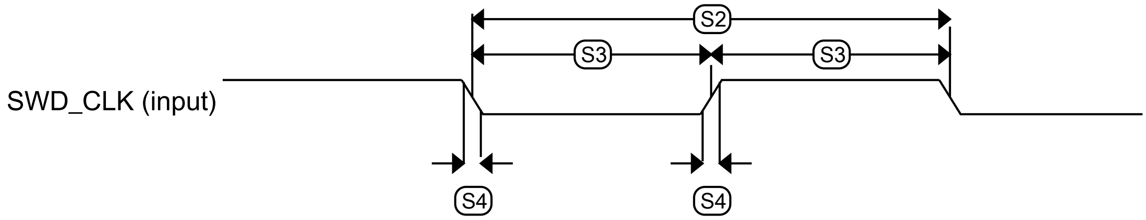


Figure 5. Serial wire clock input timing

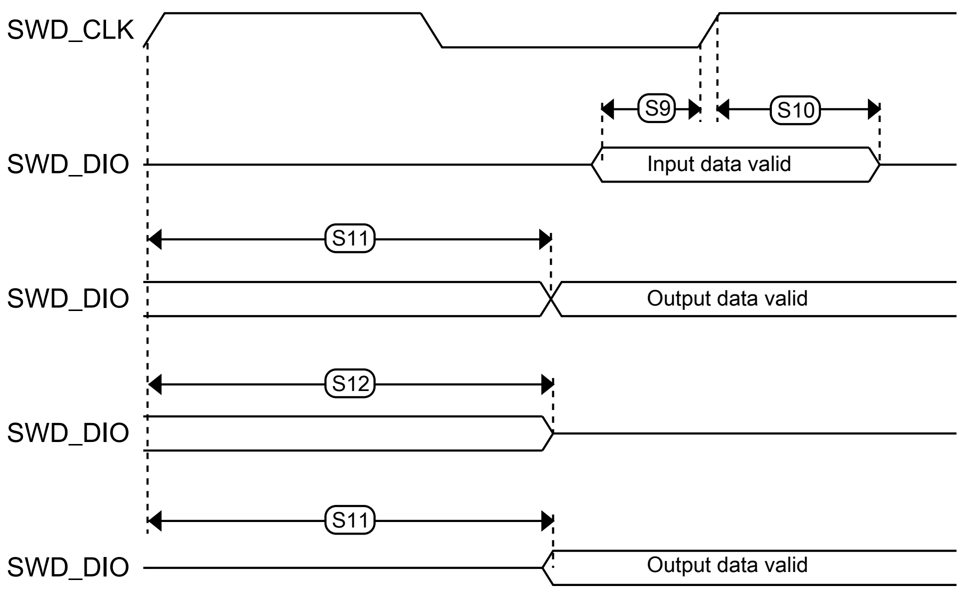


Figure 6. Serial wire data timing

3.1.2 JTAG electricals

Table 13. JTAG limited voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
J1	TCLK frequency of operation • Boundary Scan • JTAG and CJTAG	 0 0	 10 20	MHz
J2	TCLK cycle period	1/J1	—	ns
J3	TCLK clock pulse width	50	—	ns

Table continues on the next page...

Table 13. JTAG limited voltage range electricals (continued)

Symbol	Description	Min.	Max.	Unit
	• Boundary Scan • JTAG and CJTAG	25	—	ns
J4	TCLK rise and fall times	—	3	ns
J5	Boundary scan input data setup time to TCLK rise	20	—	ns
J6	Boundary scan input data hold time after TCLK rise	1	—	ns
J7	TCLK low to boundary scan output data valid	—	25	ns
J8	TCLK low to boundary scan output high-Z	—	25	ns
J9	TMS, TDI input data setup time to TCLK rise	8	—	ns
J10	TMS, TDI input data hold time after TCLK rise	1	—	ns
J11	TCLK low to TDO data valid	—	19	ns
J12	TCLK low to TDO high-Z	—	19	ns
J13	$\overline{\text{TRST}}$ assert time	100	—	ns
J14	$\overline{\text{TRST}}$ setup time (negation) to TCLK high	8	—	ns

Table 14. JTAG full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
J1	TCLK frequency of operation • Boundary Scan • JTAG and CJTAG	 0 0	 10 15	MHz
J2	TCLK cycle period	1/J1	—	ns
J3	TCLK clock pulse width • Boundary Scan • JTAG and CJTAG	 50 33	 — —	 ns ns
J4	TCLK rise and fall times	—	3	ns
J5	Boundary scan input data setup time to TCLK rise	20	—	ns
J6	Boundary scan input data hold time after TCLK rise	1.4	—	ns
J7	TCLK low to boundary scan output data valid	—	27	ns
J8	TCLK low to boundary scan output high-Z	—	27	ns
J9	TMS, TDI input data setup time to TCLK rise	8	—	ns
J10	TMS, TDI input data hold time after TCLK rise	1.4	—	ns
J11	TCLK low to TDO data valid	—	26.2	ns
J12	TCLK low to TDO high-Z	—	26.2	ns
J13	$\overline{\text{TRST}}$ assert time	100	—	ns
J14	$\overline{\text{TRST}}$ setup time (negation) to TCLK high	8	—	ns

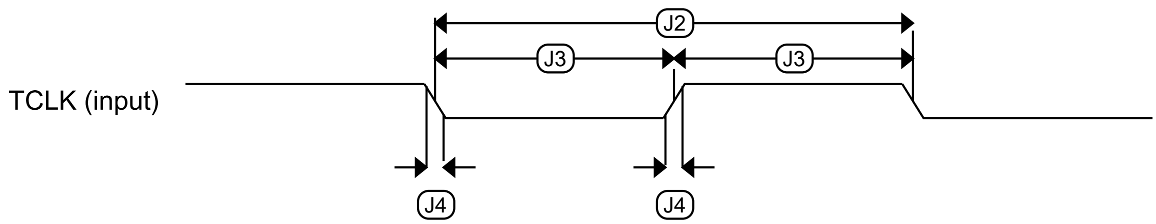


Figure 7. Test clock input timing

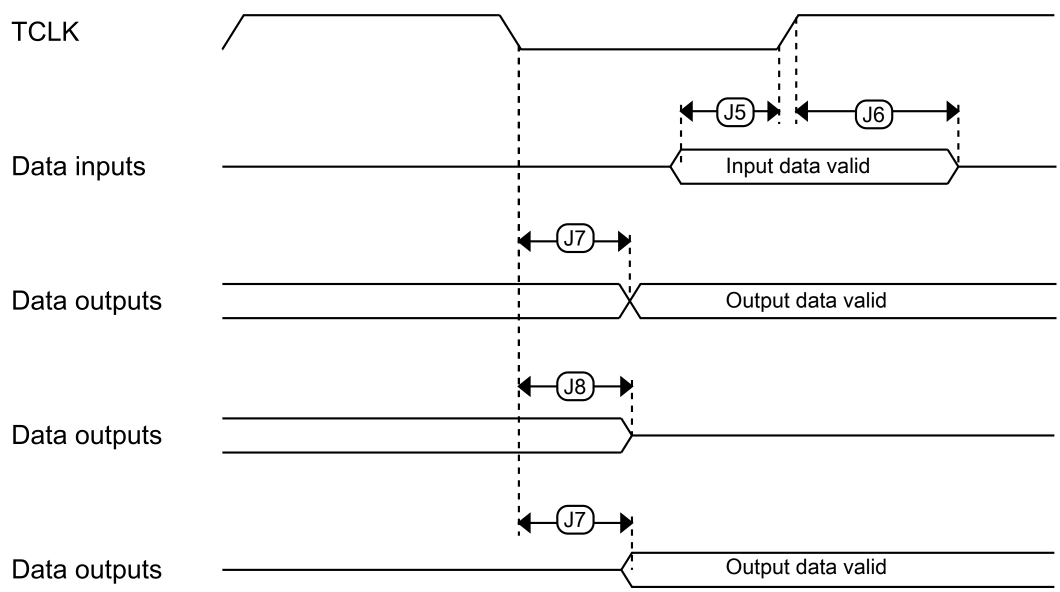


Figure 8. Boundary scan (JTAG) timing

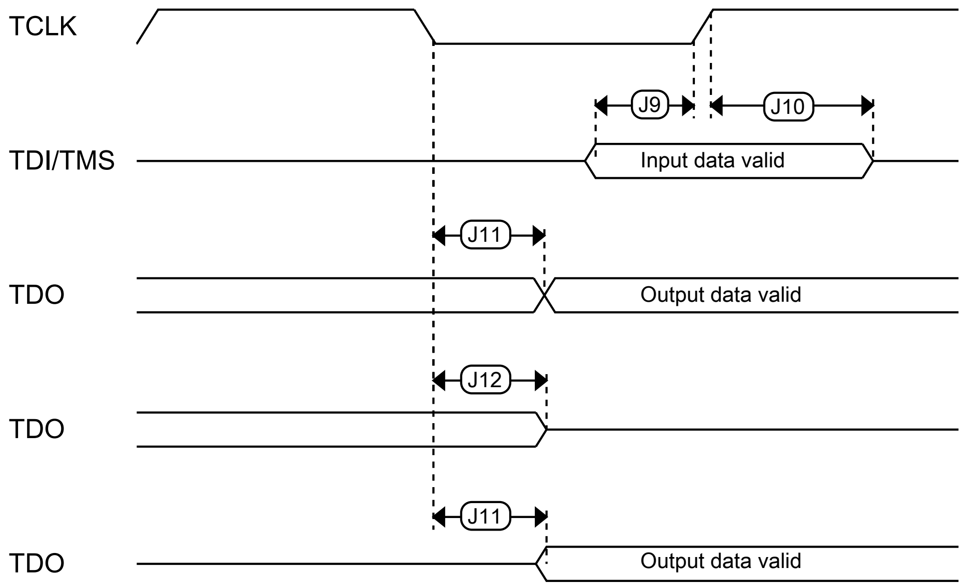


Figure 9. Test Access Port timing

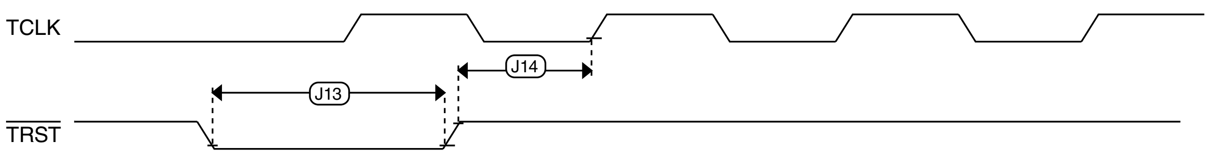


Figure 10. $\overline{TRST}$ timing

3.2 System modules

There are no specifications necessary for the device's system modules.

3.3 Clock modules

3.3.1 MCG specifications

Table 15. MCG specifications

Symbol	Description		Min.	Typ.	Max.	Unit	Notes
f_{ints_ft}	Internal reference frequency (slow clock) — factory trimmed at nominal VDD and 25 °C		—	32.768	—	kHz	
Δf_{ints_t}	Total deviation of internal reference frequency (slow clock) over voltage and temperature		—	+0.5/-0.7	± 2	%	
f_{ints_t}	Internal reference frequency (slow clock) — user trimmed		31.25	—	39.0625	kHz	
$\Delta_{fdco\_res\_t}$	Resolution of trimmed average DCO output frequency at fixed voltage and temperature — using SCTRIM and SCFTRIM		—	± 0.3	± 0.6	$\%f_{dco}$	1
Δf_{dco_t}	Total deviation of trimmed average DCO output frequency over voltage and temperature		—	+0.5/-0.7	± 2	$\%f_{dco}$	1, 2
Δf_{dco_t}	Total deviation of trimmed average DCO output frequency over fixed voltage and temperature range of 0–70°C		—	± 0.3	± 1.5	$\%f_{dco}$	1
f_{intf_ft}	Internal reference frequency (fast clock) — factory trimmed at nominal VDD and 25°C		—	4	—	MHz	
Δf_{intf_ft}	Frequency deviation of internal reference clock (fast clock) over temperature and voltage — factory trimmed at nominal VDD and 25 °C		—	+1/-2	± 5	$\%f_{intf\_ft}$	
f_{intf_t}	Internal reference frequency (fast clock) — user trimmed at nominal VDD and 25 °C		3	—	5	MHz	
f_{loc_low}	Loss of external clock minimum frequency — RANGE = 00		(3/5) x f_{ints_t}	—	—	kHz	
f_{loc_high}	Loss of external clock minimum frequency — RANGE = 01, 10, or 11		(16/5) x f_{ints_t}	—	—	kHz	
FLL							
f_{fll_ref}	FLL reference frequency range		31.25	—	39.0625	kHz	
f_{dco}	DCO output frequency range	Low range (DRS=00) $640 \times f_{fll\_ref}$	20	20.97	25	MHz	3, 4
		Mid range (DRS=01) $1280 \times f_{fll\_ref}$	40	41.94	50	MHz	
		Mid-high range (DRS=10) $1920 \times f_{fll\_ref}$	60	62.91	75	MHz	
		High range (DRS=11) $2560 \times f_{fll\_ref}$	80	83.89	100	MHz	
$f_{dco\_t\_DMX32}$	DCO output frequency	Low range (DRS=00) $732 \times f_{fll\_ref}$	—	23.99	—	MHz	5, 6
		Mid range (DRS=01) $1464 \times f_{fll\_ref}$	—	47.97	—	MHz	
		Mid-high range (DRS=10)	—	71.99	—	MHz	

Table continues on the next page...

Table 15. MCG specifications (continued)

Symbol	Description		Min.	Typ.	Max.	Unit	Notes
		$2197 \times f_{fll\_ref}$					
		High range (DRS=11) $2929 \times f_{fll\_ref}$	—	95.98	—	MHz	
J_{cyc_fll}	FLL period jitter • f_{VCO} = 48 MHz • f_{VCO} = 98 MHz		— —	— 180 150	— —	ps	
$t_{fll\_acquire}$	FLL target frequency acquisition time		—	—	1	ms	7

1. This parameter is measured with the internal reference (slow clock) being used as a reference to the FLL (FEI clock mode).
2. 2.0 V <= VDD <= 3.6 V.
3. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32=0.
4. The resulting system clock frequencies should not exceed their maximum specified values. The DCO frequency deviation (Δf_{dco_t}) over voltage and temperature should be considered.
5. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32=1.
6. The resulting clock frequency must not exceed the maximum specified clock frequency of the device.
7. This specification applies to any time the FLL reference source or reference divider is changed, trim value is changed, DMX32 bit is changed, DRS bits are changed, or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

3.3.2 IRC48M specifications

Table 16. IRC48M specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	—	3.6	V	
I_{DD48M}	Supply current	—	400	500	μA	
f_{irc48m}	Internal reference frequency	—	48	—	MHz	
$\Delta f_{irc48m\_ol\_lv}$	Open loop total deviation of IRC48M frequency at low voltage (VDD=1.71V-1.89V) over full temperature Regulator disable (USB_CLK_RECOVER_IRC_EN[REG_EN]=0) Regulator enable (USB_CLK_RECOVER_IRC_EN[REG_EN]=1)	— —	± 0.5 ± 0.5	± 1.5 ± 2.0	$\%f_{irc48m}$	
$\Delta f_{irc48m\_ol\_hv}$	Open loop total deviation of IRC48M frequency at high voltage (VDD=1.89V-3.6V) over full temperature Regulator enable (USB_CLK_RECOVER_IRC_EN[REG_EN]=1)	—	± 0.5	± 1.5	$\%f_{irc48m}$	
$\Delta f_{irc48m\_ol\_hv}$	Open loop total deviation of IRC48M frequency at high voltage (VDD=1.89V-3.6V) over -40°C to 85°C Regulator enable (USB_CLK_RECOVER_IRC_EN[REG_EN]=1)	— —	± 0.5	± 1.0	$\%f_{irc48m}$	1
Δf_{irc48m_cl}	Closed loop total deviation of IRC48M frequency over voltage and temperature	—	—	± 0.1	$\%f_{host}$	2

Table continues on the next page...

Table 16. IRC48M specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
J_{cyc_irc48m}	Period Jitter (RMS)	—	35	150	ps	
$t_{irc48mst}$	Startup time	—	2	3	μs	3

1. The maximum value represents characterized results equivalent to the mean plus or minus three times the standard deviation (mean ± 3 sigma).
2. Closed loop operation of the IRC48M is only feasible for USB device operation; it is not usable for USB host operation. It is enabled by configuring for USB Device, selecting IRC48M as USB clock source, and enabling the clock recover function (USB_CLK_RECOVER_IRC_CTRL[CLOCK_RECOVER_EN]=1, USB_CLK_RECOVER_IRC_EN[IRC_EN]=1).
3. IRC48M startup time is defined as the time between clock enablement and clock availability for system use. Enable the clock by one of the following settings:
    - USB_CLK_RECOVER_IRC_EN[IRC_EN]=1, or
    - MCG operating in an external clocking mode and MCG_C7[OSCSEL]=10, or
    - SIM_SOPT2[PLLFLLSEL]=11

3.3.3 Oscillator electrical specifications

3.3.3.1 Oscillator DC electrical specifications

Table 17. Oscillator DC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	—	3.6	V	
I_{DDOSC}	Supply current — low-power mode (HGO=0)					1
	• 32 kHz	—	500	—	nA	
	• 4 MHz	—	200	—	μA	
	• 8 MHz (RANGE=01)	—	300	—	μA	
	• 16 MHz	—	950	—	μA	
	• 24 MHz	—	1.2	—	mA	
	• 32 MHz	—	1.5	—	mA	
I_{DDOSC}	Supply current — high-gain mode (HGO=1)					1
	• 32 kHz	—	25	—	μA	
	• 4 MHz	—	400	—	μA	
	• 8 MHz (RANGE=01)	—	500	—	μA	
	• 16 MHz	—	2.5	—	mA	
	• 24 MHz	—	3	—	mA	
	• 32 MHz	—	4	—	mA	
C_x	EXTAL load capacitance	—	—	—		2, 3
C_y	XTAL load capacitance	—	—	—		2, 3

Table continues on the next page...

Table 17. Oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
R_F	Feedback resistor — low-frequency, low-power mode (HGO=0)	—	—	—	MΩ	2, 4
	Feedback resistor — low-frequency, high-gain mode (HGO=1)	—	10	—	MΩ	
	Feedback resistor — high-frequency, low-power mode (HGO=0)	—	—	—	MΩ	
	Feedback resistor — high-frequency, high-gain mode (HGO=1)	—	1	—	MΩ	
R_S	Series resistor — low-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — low-frequency, high-gain mode (HGO=1)	—	200	—	kΩ	
	Series resistor — high-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — high-frequency, high-gain mode (HGO=1)	—	0	—	kΩ	
V_{pp}[5]	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	

1. V_{DD}=3.3 V, Temperature =25 °C
2. See crystal or resonator manufacturer's recommendation
3. C_x and C_y can be provided by using either integrated capacitors or external components.
4. When low-power mode is selected, R_F is integrated and must not be attached externally.
5. The EXTAL and XTAL pins should only be connected to required oscillator components and must not be connected to any other device.

3.3.3.2 Oscillator frequency specifications

Table 18. Oscillator frequency specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{osc_lo}	Oscillator crystal or resonator frequency — low-frequency mode (MCG_C2[RANGE]=00)	32	—	40	kHz	

Table continues on the next page...

Table 18. Oscillator frequency specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$f_{osc\_hi\_1}$	Oscillator crystal or resonator frequency — high-frequency mode (low range) (MCG_C2[RANGE]=01)	3	—	8	MHz	
$f_{osc\_hi\_2}$	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	8	—	32	MHz	
f_{ec_extal}	Input clock frequency (external clock mode)	—	—	50	MHz	1, 2
t_{dc_extal}	Input clock duty cycle (external clock mode)	40	50	60	%	
t_{cst}	Crystal startup time — 32 kHz low-frequency, low-power mode (HGO=0)	—	750	—	ms	3, 4
	Crystal startup time — 32 kHz low-frequency, high-gain mode (HGO=1)	—	250	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), low-power mode (HGO=0)	—	0.6	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), high-gain mode (HGO=1)	—	1	—	ms	

1. Other frequency limits may apply when external clock is being used as a reference for the FLL
2. When transitioning from FEI or FBI to FBE mode, restrict the frequency of the input clock so that, when it is divided by FRDIV, it remains within the limits of the DCO input clock frequency.
3. Proper PC board layout procedures must be followed to achieve specifications.
4. Crystal startup time is defined as the time between the oscillator being enabled and the OSCINIT bit in the MCG_S register being set.

3.3.4 32 kHz oscillator electrical characteristics

3.3.4.1 32 kHz oscillator DC electrical specifications

Table 19. 32kHz oscillator DC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{BAT}	Supply voltage	1.71	—	3.6	V
R_F	Internal feedback resistor	—	100	—	MΩ
C_{para}	Parasitical capacitance of EXTAL32 and XTAL32	—	5	7	pF
V_{pp}[1]	Peak-to-peak amplitude of oscillation	—	0.6	—	V

1. When a crystal is being used with the 32 kHz oscillator, the EXTAL32 and XTAL32 pins should only be connected to required oscillator components and must not be connected to any other devices.

3.3.4.2 32 kHz oscillator frequency specifications

Table 20. 32 kHz oscillator frequency specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{osc_lo}	Oscillator crystal	—	32.768	—	kHz	
t_{start}	Crystal start-up time	—	1000	—	ms	1
$f_{ec\_extal32}$	Externally provided input clock frequency	—	32.768	—	kHz	2
$v_{ec\_extal32}$	Externally provided input clock amplitude	700	—	V_{BAT}	mV	2, 3

1. Proper PC board layout procedures must be followed to achieve specifications.
2. This specification is for an externally supplied clock driven to EXTAL32 and does not apply to any other clock input. The oscillator remains enabled and XTAL32 must be left unconnected.
3. The parameter specified is a peak-to-peak value and V_{IH} and V_{IL} specifications do not apply. The voltage of the applied clock must be within the range of V_{SS} to V_{BAT}.

3.4 Memories and memory interfaces

3.4.1 Flash electrical specifications

This section describes the electrical characteristics of the flash memory module.

3.4.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Table 21. NVM program/erase timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{hvpgm4}	Longword Program high-voltage time	—	7.5	18	μs	—
$t_{hversscr}$	Sector Erase high-voltage time	—	13	113	ms	1
$t_{hversall}$	Erase All high-voltage time	—	52	452	ms	1

1. Maximum time based on expectations at cycling end-of-life.

3.4.1.2 Flash timing specifications — commands

Table 22. Flash command timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{rd1sec2k}$	Read 1s Section execution time (flash sector)	—	—	60	μs	1
t_{pgmchk}	Program Check execution time	—	—	45	μs	1

Table continues on the next page...

Table 22. Flash command timing specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{rdrsrc}	Read Resource execution time	—	—	30	μs	1
t_{pgm4}	Program Longword execution time	—	65	145	μs	—
t_{ersscr}	Erase Flash Sector execution time	—	14	114	ms	2
t_{rd1all}	Read 1s All Blocks execution time	—	—	0.9	ms	1
t_{rdonce}	Read Once execution time	—	—	30	μs	1
$t_{pgmonce}$	Program Once execution time	—	100	—	μs	—
t_{ersall}	Erase All Blocks execution time	—	140	1150	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	μs	1

1. Assumes 25 MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.

3.4.1.3 Flash high voltage current behaviors

Table 23. Flash high voltage current behaviors

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DD_PGM}	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
I_{DD_ERS}	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

3.4.1.4 Reliability specifications

Table 24. NVM reliability specifications

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
	Program Flash					
$t_{nvmretp10k}$	Data retention after up to 10 K cycles	5	50	—	years	—
$t_{nvmretp1k}$	Data retention after up to 1 K cycles	20	100	—	years	—
$n_{nvmcycp}$	Cycling endurance	10 K	50 K	—	cycles	2

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25 °C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.
2. Cycling endurance represents number of program/erase cycles at –40 °C ≤ T_j ≤ 125 °C.

3.4.2 EzPort switching specifications

Table 25. EzPort switching specifications

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
EP1	EZP_CK frequency of operation (all commands except READ)	—	$f_{SYS}/2$	MHz
EP1a	EZP_CK frequency of operation (READ command)	—	$f_{SYS}/8$	MHz
EP2	EZP_CS negation to next EZP_CS assertion	2 x t_{EZP_CK}	—	ns
EP3	EZP_CS input valid to EZP_CK high (setup)	5	—	ns
EP4	EZP_CK high to EZP_CS input invalid (hold)	5	—	ns
EP5	EZP_D input valid to EZP_CK high (setup)	2	—	ns
EP6	EZP_CK high to EZP_D input invalid (hold)	5	—	ns
EP7	EZP_CK low to EZP_Q output valid	—	25	ns
EP8	EZP_CK low to EZP_Q output invalid (hold)	0	—	ns
EP9	EZP_CS negation to EZP_Q tri-state	—	12	ns

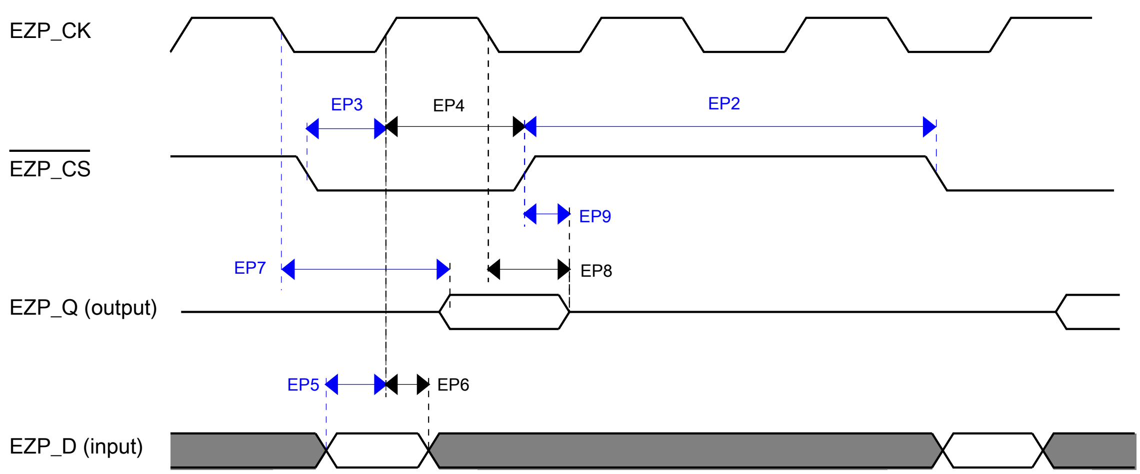


Figure 11. EzPort Timing Diagram

3.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

3.6 Analog

3.6.1 ADC electrical specifications

The 16-bit accuracy specifications listed in Table 26 and Table 27 are achievable on the differential pins ADCx_DPx, ADCx_DMx.

All other ADC channels meet the 13-bit differential/12-bit single-ended accuracy specifications.

3.6.1.1 16-bit ADC operating conditions

Table 26. 16-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
V_{DDA}	Supply voltage	Absolute	1.71	—	3.6	V	
ΔV_{DDA}	Supply voltage	Delta to V_{DD} ($V_{DD} – V_{DDA}$)	-100	0	+100	mV	2
ΔV_{SSA}	Ground voltage	Delta to V_{SS} ($V_{SS} – V_{SSA}$)	-100	0	+100	mV	2
V_{REFH}	ADC reference voltage high		1.13	V_{DDA}	V_{DDA}	V	
V_{REFL}	ADC reference voltage low		V_{SSA}	V_{SSA}	V_{SSA}	V	
V_{ADIN}	Input voltage	• 16-bit differential mode • All other modes	VREFL VREFL	— —	31/32 * VREFH VREFH	V	
C_{ADIN}	Input capacitance	• 16-bit mode • 8-bit / 10-bit / 12-bit modes	— —	8 4	10 5	pF	
R_{ADIN}	Input series resistance		—	2	5	kΩ	
R_{AS}	Analog source resistance (external)	13-bit / 12-bit modes f_{ADCK} < 4 MHz	—	—	5	kΩ	3
f_{ADCK}	ADC conversion clock frequency	≤ 13-bit mode	1.0	—	24.0	MHz	4
f_{ADCK}	ADC conversion clock frequency	16-bit mode	2.0	—	12.0	MHz	4
C_{rate}	ADC conversion rate	≤ 13-bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20	—	1200	Ksps	5

Table continues on the next page...

Table 26. 16-bit ADC operating conditions (continued)

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
C_{rate}	ADC conversion rate	16-bit mode No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	37	—	461	Ksps	5

1. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz, unless otherwise stated. Typical values are for reference only, and are not tested in production.
2. DC potential difference.
3. This resistance is external to MCU. To achieve the best results, the analog source resistance must be kept as low as possible. The results in this data sheet were derived from a system that had < 8 Ω analog source resistance. The R_{AS}/C_{AS} time constant should be kept to < 1 ns.
4. To use the maximum ADC conversion clock frequency, CFG2[ADHSC] must be set and CFG1[ADLPC] must be clear.
5. For guidelines and examples of conversion rate calculation, download the ADC calculator tool.

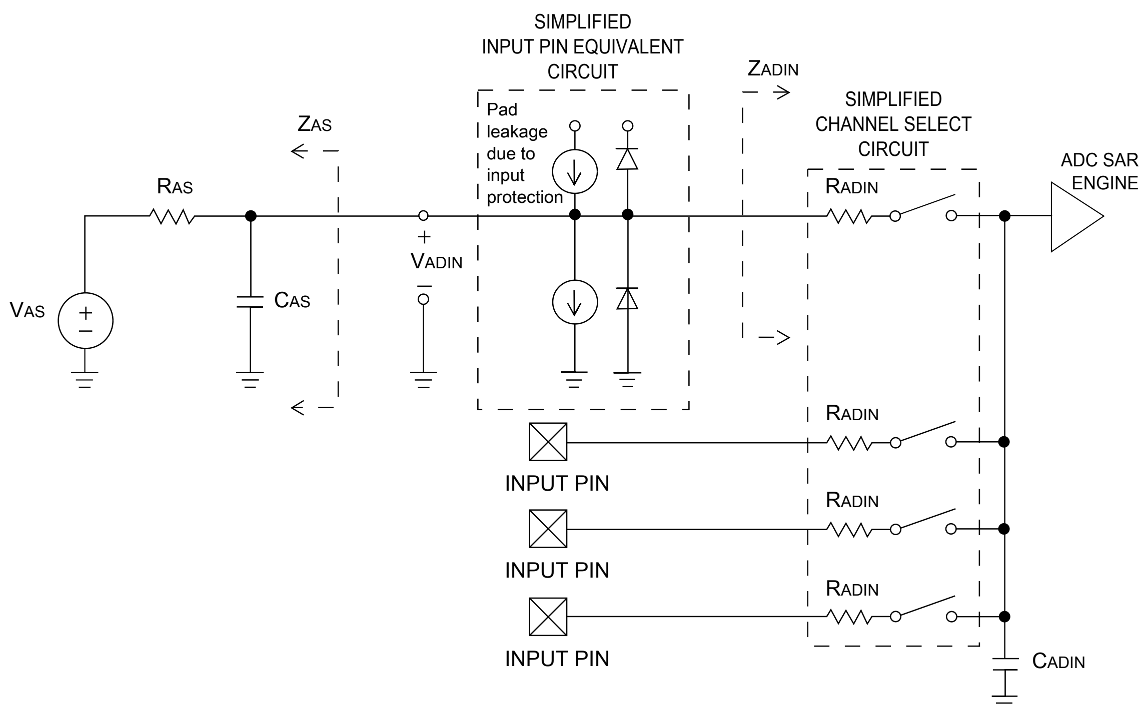


Figure 12. ADC input impedance equivalency diagram

3.6.1.2 16-bit ADC electrical characteristics

Table 27. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$)

Symbol	Description	Conditions[1]	Min.	Typ.[2]	Max.	Unit	Notes
I_{DDA_ADC}	Supply current		0.215	—	1.7	mA	3
f_{ADACK}	ADC asynchronous clock source	• ADLPC = 1, ADHSC = 0 • ADLPC = 1, ADHSC = 1 • ADLPC = 0, ADHSC = 0 • ADLPC = 0, ADHSC = 1	1.2 2.4 3.0 4.4	2.4 4.0 5.2 6.2	3.9 6.1 7.3 9.5	MHz MHz MHz MHz	$t_{ADACK} = 1/f_{ADACK}$
	Sample Time	See Reference Manual chapter for sample times					
TUE	Total unadjusted error	• 12-bit modes • <12-bit modes	— —	±4 ±1.4	±6.8 ±2.1	LSB[4]	5
DNL	Differential non-linearity	• 12-bit modes • <12-bit modes	— —	±0.7 ±0.2	–1.1 to +1.9 –0.3 to 0.5	LSB[4]	5
INL	Integral non-linearity	• 12-bit modes • <12-bit modes	— —	±1.0 ±0.5	–2.7 to +1.9 –0.7 to +0.5	LSB[4]	5
E_{FS}	Full-scale error	• 12-bit modes • <12-bit modes	— —	–4 –1.4	–5.4 –1.8	LSB[4]	$V_{ADIN} = V_{DDA}$[5]
E_Q	Quantization error	• 16-bit modes • ≤13-bit modes	— —	–1 to 0 —	— ±0.5	LSB[4]	
ENOB	Effective number of bits	16-bit differential mode • Avg = 32 • Avg = 4 16-bit single-ended mode • Avg = 32 • Avg = 4	12.8 11.9 12.2 11.4	14.5 13.8 13.9 13.1	— — — —	bits bits bits bits	6
SINAD	Signal-to-noise plus distortion	See ENOB	$6.02 \times ENOB + 1.76$			dB	
THD	Total harmonic distortion	16-bit differential mode • Avg = 32 16-bit single-ended mode • Avg = 32	— —	-94 -85	— —	dB dB	7
SFDR	Spurious free dynamic range	16-bit differential mode • Avg = 32 16-bit single-ended mode	82 78	95 90	— —	dB dB	7

Table continues on the next page...

Table 27. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Symbol	Description	Conditions[1]	Min.	Typ.[2]	Max.	Unit	Notes
		• Avg = 32					
E_{IL}	Input leakage error			$I_{In} \times R_{AS}$		mV	I_{In} = leakage current (refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	Across the full temperature range of the device	1.55	1.62	1.69	mV/°C	8
V_{TEMP25}	Temp sensor voltage	25 °C	706	716	726	mV	8

1. All accuracy numbers assume the ADC is calibrated with $V_{REFH} = V_{DDA}$
2. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 2.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
3. The ADC supply current depends on the ADC conversion clock speed, conversion rate and ADC_CFG1[ADLPC] (low power). For lowest power operation, ADC_CFG1[ADLPC] must be set, the ADC_CFG2[ADHSC] bit must be clear with 1 MHz ADC conversion clock speed.
4. 1 LSB = $(V_{REFH} - V_{REFL})/2^N$
5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
6. Input data is 100 Hz sine wave. ADC conversion clock < 12 MHz.
7. Input data is 1 kHz sine wave. ADC conversion clock < 12 MHz.
8. ADC conversion clock < 3 MHz

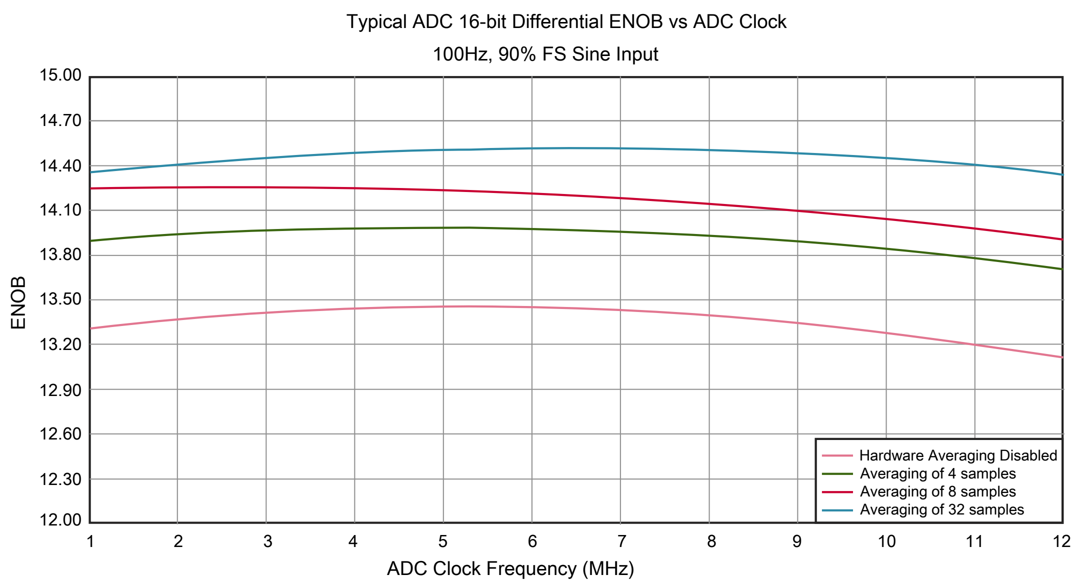


Figure 13. Typical ENOB vs. ADC_CLK for 16-bit differential mode

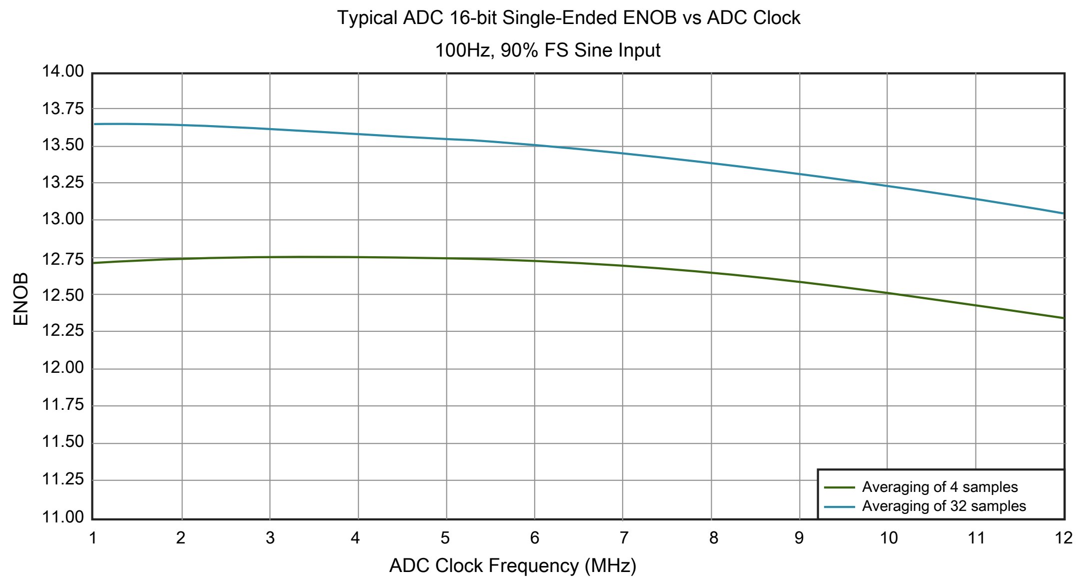


Figure 14. Typical ENOB vs. ADC_CLK for 16-bit single-ended mode

3.6.2 CMP and 6-bit DAC electrical specifications

Table 28. Comparator and 6-bit DAC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{DD}	Supply voltage	1.71	—	3.6	V
I_{DDHS}	Supply current, High-speed mode (EN=1, PMODE=1)	—	—	200	μA
I_{DDLS}	Supply current, low-speed mode (EN=1, PMODE=0)	—	—	20	μA
V_{AIN}	Analog input voltage	V_{SS} – 0.3	—	V_{DD}	V
V_{AIO}	Analog input offset voltage	—	—	20	mV
V_H	Analog comparator hysteresis[1]				
	• CR0[HYSTCTR] = 00	—	5	—	mV
	• CR0[HYSTCTR] = 01	—	10	—	mV
	• CR0[HYSTCTR] = 10	—	20	—	mV
	• CR0[HYSTCTR] = 11	—	30	—	mV
V_{CMPOh}	Output high	V_{DD} – 0.5	—	—	V
V_{CMPOl}	Output low	—	—	0.5	V
t_{DHS}	Propagation delay, high-speed mode (EN=1, PMODE=1)	20	50	200	ns
t_{DLS}	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay[2]	—	—	40	μs
I_{DAC6b}	6-bit DAC current adder (enabled)	—	7	—	μA
INL	6-bit DAC integral non-linearity	–0.5	—	0.5	LSB[3]
DNL	6-bit DAC differential non-linearity	–0.3	—	0.3	LSB

1. Typical hysteresis is measured with input voltage range limited to 0.6 to V_{DD}–0.6 V.
2. Comparator initialization delay is defined as the time between software writes to change control inputs (Writes to CMP_DACCR[DACEN], CMP_DACCR[VRSEL], CMP_DACCR[VOSEL], CMP_MUXCR[PSEL], and CMP_MUXCR[MSEL]) and the comparator output settling to a stable level.
3. 1 LSB = $V_{reference}$/64

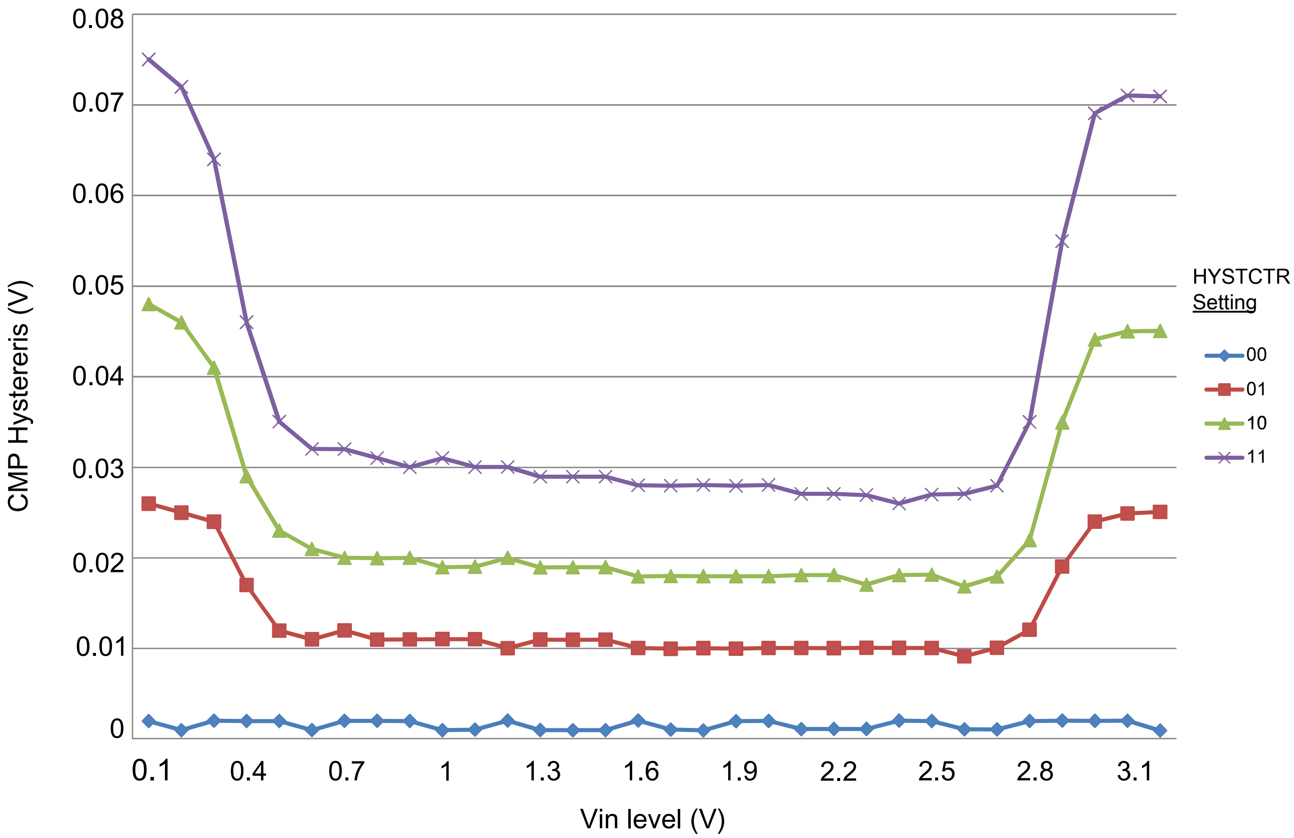


Figure 15. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 0)

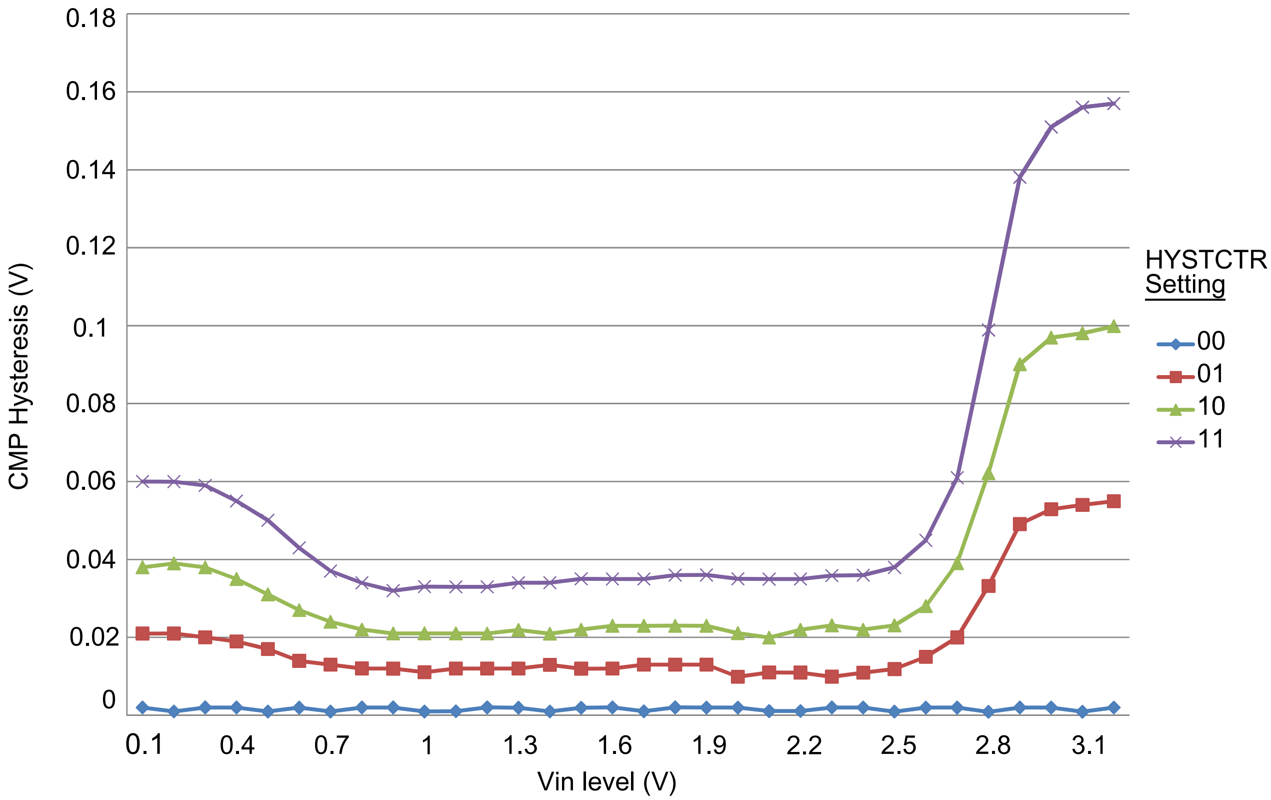


Figure 16. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 1)

3.6.3 12-bit DAC electrical characteristics

The 12-bit DAC output (DAC0_OUT) is not available on an external pin and is limited to internal connections to CMP1 analog input and ADC0 channel input.

3.6.3.1 12-bit DAC operating requirements

Table 29. 12-bit DAC operating requirements

Symbol	Desciption	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage	1.71	3.6	V	
V_{DACR}	Reference voltage	1.13	3.6	V	1
C_L	Output load capacitance	—	100	pF	2
I_L	Output load current	—	1	mA	

1. The DAC reference can be selected to be V_{DDA} or V_{REFH}.
2. A small load capacitance (47 pF) can improve the bandwidth performance of the DAC.

3.6.3.2 12-bit DAC operating behaviors

Table 30. 12-bit DAC operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA_DACLP}	Supply current — low-power mode	—	—	330	μA	
I_{DDA_DACHP}	Supply current — high-speed mode	—	—	1200	μA	
t_{DACLP}	Full-scale settling time (0x080 to 0xF7F) — low-power mode	—	100	200	μs	1
t_{DACHP}	Full-scale settling time (0x080 to 0xF7F) — high-power mode	—	15	30	μs	1
$t_{CCDACLP}$	Code-to-code settling time (0xBF8 to 0xC08) — low-power mode and high-speed mode	—	0.7	1	μs	1
$V_{dacoutl}$	DAC output voltage range low — high-speed mode, no load, DAC set to 0x000	—	—	100	mV	
$V_{dacouth}$	DAC output voltage range high — high-speed mode, no load, DAC set to 0xFFF	V_{DACR} −100	—	V_{DACR}	mV	
INL	Integral non-linearity error — high speed mode	—	—	±8	LSB	2
DNL	Differential non-linearity error — V_{DACR} > 2 V	—	—	±1	LSB	3
DNL	Differential non-linearity error — V_{DACR} = VREF_OUT	—	—	±1	LSB	4
V_{OFFSET}	Offset error	—	±0.4	±0.8	%FSR	5
E_G	Gain error	—	±0.1	±0.6	%FSR	5
PSRR	Power supply rejection ratio, V_{DDA} ≥ 2.4 V	60	—	90	dB	
T_{CO}	Temperature coefficient offset voltage	—	3.7	—	μV/C	6
T_{GE}	Temperature coefficient gain error	—	0.000421	—	%FSR/C	
Rop	Output resistance (load = 3 kΩ)	—	—	250	Ω	
SR	Slew rate -80h→ F7Fh→ 80h				V/μs	
	• High power (SP_{HP})	1.2	1.7	—		
	• Low power (SP_{LP})	0.05	0.12	—		
BW	3dB bandwidth				kHz	
	• High power (SP_{HP})	550	—	—		
	• Low power (SP_{LP})	40	—	—		

1. Settling within ±1 LSB
2. The INL is measured for 0 + 100 mV to V_{DACR} −100 mV
3. The DNL is measured for 0 + 100 mV to V_{DACR} −100 mV
4. The DNL is measured for 0 + 100 mV to V_{DACR} −100 mV with V_{DDA} > 2.4 V
5. Calculated by a best fit curve from V_{SS} + 100 mV to V_{DACR} − 100 mV
6. V_{DDA} = 3.0 V, reference select set for V_{DDA} (DACx_CO:DACRFS = 1), high power mode (DACx_C0:LPEN = 0), DAC set to 0x800, temperature range is across the full range of the device

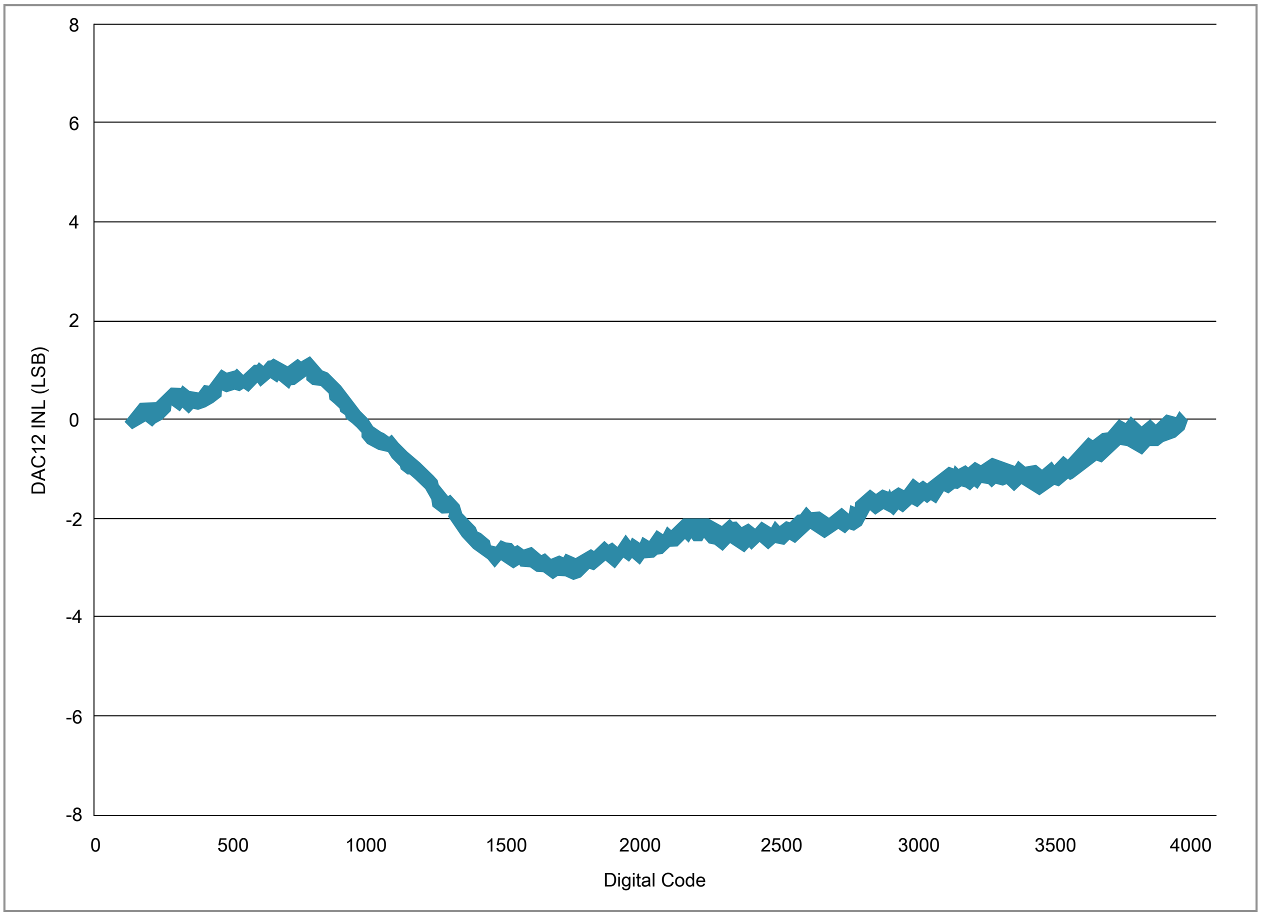


Figure 17. Typical INL error vs. digital code

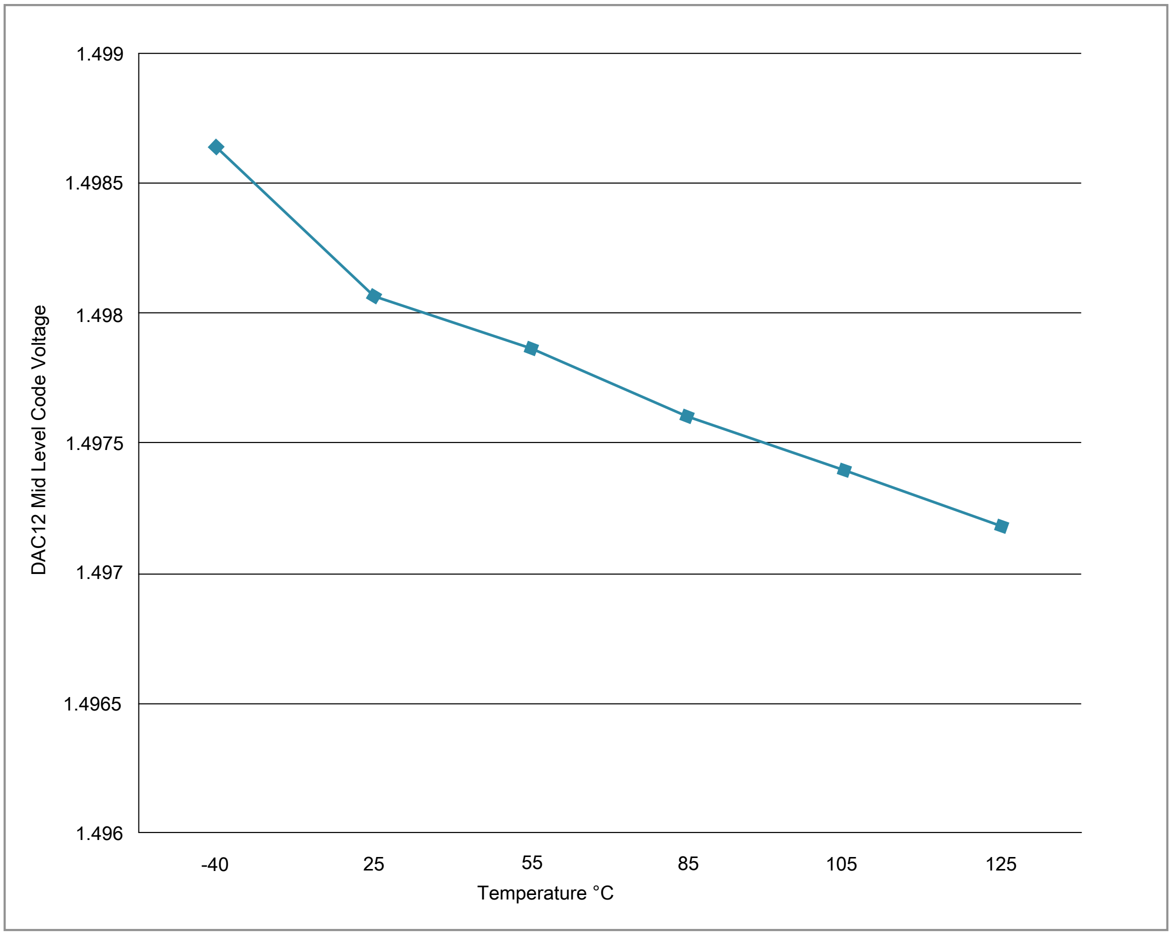


Figure 18. Offset at half scale vs. temperature

3.6.4 Voltage reference electrical specifications

Table 31. VREF full-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage	1.71	3.6	V	
T_A	Temperature	Operating temperature range of the device		°C	
C_L	Output load capacitance	100		nF	1, 2

1. C_L must be connected to VREF_OUT if the VREF_OUT functionality is being used for either an internal or external reference.
2. The load capacitance should not exceed +/-25% of the nominal specified C_L value over the operating temperature range of the device.

Table 32. VREF full-range operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{out}	Voltage reference output with factory trim at nominal V_{DDA} and temperature=25°C	1.1920	1.1950	1.1980	V	1
V_{out}	Voltage reference output with user trim at nominal V_{DDA} and temperature=25°C	1.1945	1.1950	1.1955	V	1
V_{step}	Voltage reference trim step	—	0.5	—	mV	1
V_{tdrift}	Temperature drift (Vmax -Vmin across the full temperature range)	—	—	15	mV	1
I_{bg}	Bandgap only current	—	—	80	µA	
I_{lp}	Low-power buffer current	—	—	360	uA	1
I_{hp}	High-power buffer current	—	—	1	mA	1
ΔV_{LOAD}	Load regulation • current = ± 1.0 mA	—	200	—	µV	1, 2
T_{stup}	Buffer startup time	—	—	100	µs	
$T_{chop\_osc\_stup}$	Internal bandgap start-up delay with chop oscillator enabled	—	—	35	ms	
V_{vdrift}	Voltage drift (Vmax -Vmin across the full voltage range)	—	2	—	mV	1

1. See the chip's Reference Manual for the appropriate settings of the VREF Status and Control register.
2. Load regulation voltage is the difference between the VREF_OUT voltage with no load vs. voltage with defined load

Table 33. VREF limited-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
T_A	Temperature	0	70	°C	

Table 34. VREF limited-range operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V_{tdrift}	Temperature drift (V_{max} -V_{min} across the limited temperature range)	—	10	mV	

3.7 Timers

See General switching specifications.

3.8 Communication interfaces

3.8.1 USB electrical specifications

The USB electricals for the USB On-the-Go module conform to the standards documented by the Universal Serial Bus Implementers Forum. For the most up-to-date standards, visit **usb.org**.

NOTE

The MCGFLLCLK does not meet the USB jitter specifications for certification.

The IRC48M meets the USB jitter specifications for certification in Device mode when the USB clock recovery mode is enabled. It does not meet the USB jitter specifications for certification in Host mode operation.

This device does not have the USB_CLKIN signal available and therefore cannot support Host mode operation.

3.8.2 DSPI switching specifications (limited voltage range)

The Deserial Serial Peripheral Interface (DSPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The tables below provide DSPI timing characteristics for classic SPI timing modes. Refer to the SPI chapter of the Reference Manual for information on the modified transfer formats used for communicating with slower peripheral devices.

Table 35. Master mode DSPI timing (limited voltage range)

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	2.7	3.6	V	
	Frequency of operation	—	25	MHz	
DS1	DSPI_SCK output cycle time	$2 \times t_{BUS}$	—	ns	
DS2	DSPI_SCK output high/low time	$(t_{SCK}/2) - 2$	$(t_{SCK}/2) + 2$	ns	
DS3	DSPI_PCS*n* valid to DSPI_SCK delay	$(t_{BUS} \times 2) - 2$	—	ns	1
DS4	DSPI_SCK to DSPI_PCS*n* invalid delay	$(t_{BUS} \times 2) - 2$	—	ns	2
DS5	DSPI_SCK to DSPI_SOUT valid	—	8.5	ns	
DS6	DSPI_SCK to DSPI_SOUT invalid	-2	—	ns	
DS7	DSPI_SIN to DSPI_SCK input setup	16.2	—	ns	
DS8	DSPI_SCK to DSPI_SIN input hold	0	—	ns	

1. The delay is programmable in SPIx_CTARn[PSSCK] and SPIx_CTARn[CSSCK].
2. The delay is programmable in SPIx_CTARn[PASC] and SPIx_CTARn[ASC].

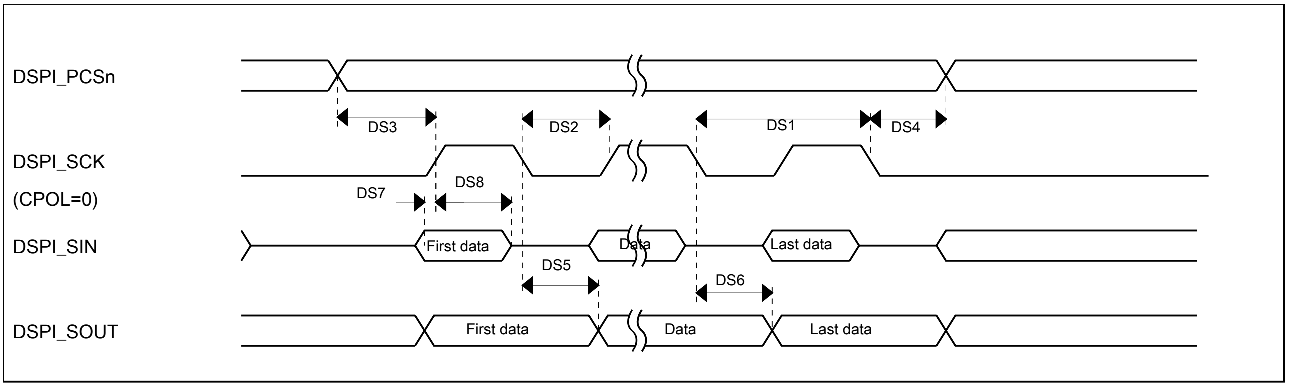


Figure 19. DSPI classic SPI timing — master mode

Table 36. Slave mode DSPI timing (limited voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
	Frequency of operation	—	12.5	MHz
DS9	DSPI_SCK input cycle time	4 x t_{BUS}	—	ns
DS10	DSPI_SCK input high/low time	$(t_{SCK}/2) - 2$	$(t_{SCK}/2) + 2$	ns
DS11	DSPI_SCK to DSPI_SOUT valid	—	21.4	ns
DS12	DSPI_SCK to DSPI_SOUT invalid	0	—	ns
DS13	DSPI_SIN to DSPI_SCK input setup	2.6	—	ns
DS14	DSPI_SCK to DSPI_SIN input hold	7	—	ns
DS15	$\overline{\text{DSPI\_SS}}$ active to DSPI_SOUT driven	—	17	ns
DS16	$\overline{\text{DSPI\_SS}}$ inactive to DSPI_SOUT not driven	—	17	ns

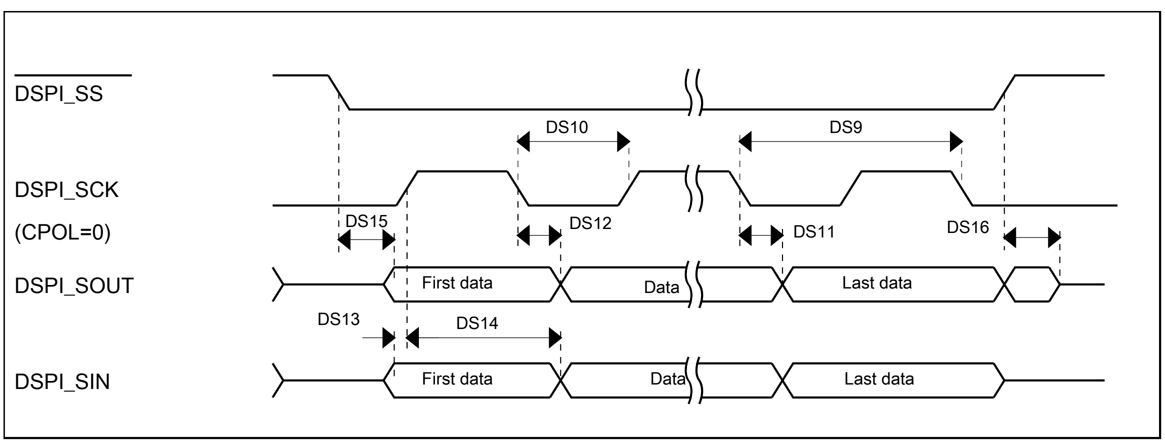


Figure 20. DSPI classic SPI timing — slave mode

3.8.3 DSPI switching specifications (full voltage range)

The Deserial Serial Peripheral Interface (DSPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The tables below provides DSPI timing characteristics for classic SPI timing modes. Refer to the SPI chapter of the Reference Manual for information on the modified transfer formats used for communicating with slower peripheral devices.

Table 37. Master mode DSPI timing (full voltage range)

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	1.71	3.6	V	1
	Frequency of operation	—	12.5	MHz	
DS1	DSPI_SCK output cycle time	4 x t_{BUS}	—	ns	
DS2	DSPI_SCK output high/low time	(t_{SCK}/2) - 4	($t_{SCK/2)}$ + 4	ns	
DS3	DSPI_PCS*n* valid to DSPI_SCK delay	(t_{BUS} x 2) – 4	—	ns	2
DS4	DSPI_SCK to DSPI_PCS*n* invalid delay	(t_{BUS} x 2) – 4	—	ns	3
DS5	DSPI_SCK to DSPI_SOUT valid	—	10	ns	
DS6	DSPI_SCK to DSPI_SOUT invalid	-4.5	—	ns	
DS7	DSPI_SIN to DSPI_SCK input setup	24.6	—	ns	
DS8	DSPI_SCK to DSPI_SIN input hold	0	—	ns	

1. The DSPI module can operate across the entire operating voltage for the processor, but to run across the full voltage range the maximum frequency of operation is reduced.
2. The delay is programmable in SPIx_CTARn[PSSCK] and SPIx_CTARn[CSSCK].
3. The delay is programmable in SPIx_CTARn[PASC] and SPIx_CTARn[ASC].

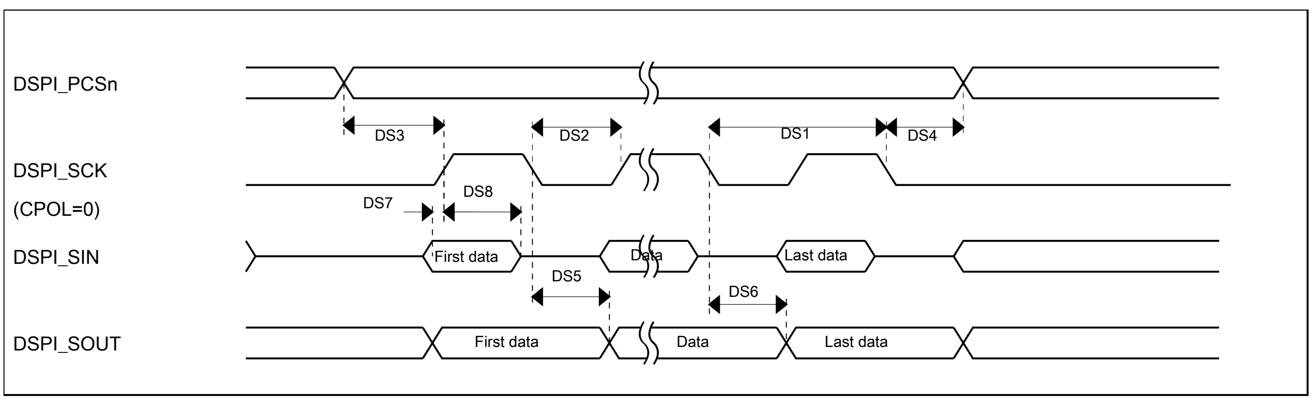


Figure 21. DSPI classic SPI timing — master mode

Table 38. Slave mode DSPI timing (full voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
	Frequency of operation	—	6.25	MHz
DS9	DSPI_SCK input cycle time	8 x t_{BUS}	—	ns
DS10	DSPI_SCK input high/low time	$(t_{SCK}/2) - 4$	$(t_{SCK/2)} + 4$	ns
DS11	DSPI_SCK to DSPI_SOUT valid	—	29.5	ns
DS12	DSPI_SCK to DSPI_SOUT invalid	0	—	ns
DS13	DSPI_SIN to DSPI_SCK input setup	3.2	—	ns
DS14	DSPI_SCK to DSPI_SIN input hold	7	—	ns
DS15	$\overline{\text{DSPI\_SS}}$ active to DSPI_SOUT driven	—	25	ns
DS16	$\overline{\text{DSPI\_SS}}$ inactive to DSPI_SOUT not driven	—	25	ns

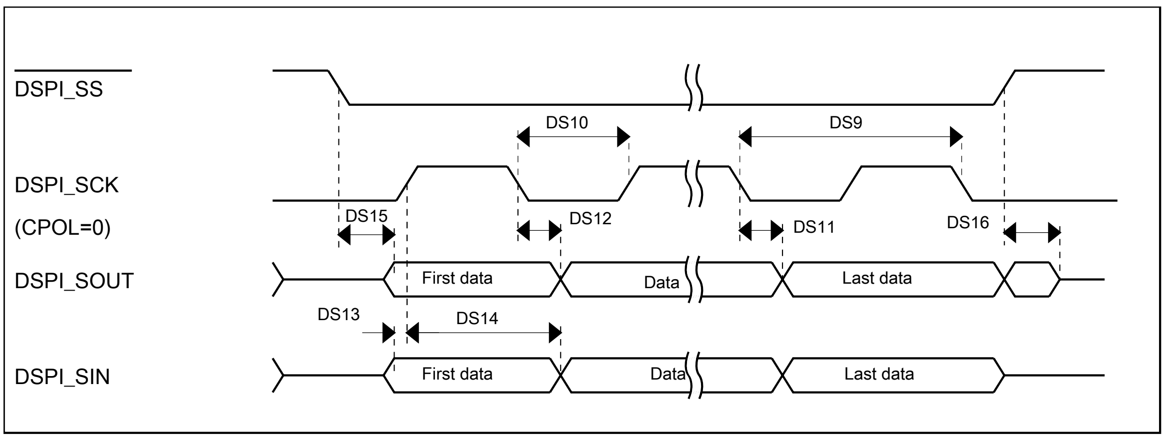


Figure 22. DSPI classic SPI timing — slave mode

3.8.4 Inter-Integrated Circuit Interface (I^2C) timing

Table 39. I^2C timing

Characteristic	Symbol	Standard Mode		Fast Mode		Unit
		Minimum	Maximum	Minimum	Maximum	
SCL Clock Frequency	f_{SCL}	0	100	0	400[1]	kHz
Hold time (repeated) START condition. After this period, the first clock pulse is generated.	t_{HD}; STA	4	—	0.6	—	µs
LOW period of the SCL clock	t_{LOW}	4.7	—	1.25	—	µs
HIGH period of the SCL clock	t_{HIGH}	4	—	0.6	—	µs
Set-up time for a repeated START condition	t_{SU}; STA	4.7	—	0.6	—	µs

Table continues on the next page...

Table 39. I²C timing (continued)

Characteristic	Symbol	Standard Mode		Fast Mode		Unit
		Minimum	Maximum	Minimum	Maximum	
Data hold time for I²C bus devices	t_{HD}; DAT	0[2]	3.45[3]	0[4]	0.9[2]	µs
Data set-up time	t_{SU}; DAT	250[5]	—	100[3, 6]	—	ns
Rise time of SDA and SCL signals	t_r	—	1000	20 +0.1C_b[7]	300	ns
Fall time of SDA and SCL signals	t_f	—	300	20 +0.1C_b[6]	300	ns
Set-up time for STOP condition	t_{SU}; STO	4	—	0.6	—	µs
Bus free time between STOP and START condition	t_{BUF}	4.7	—	1.3	—	µs
Pulse width of spikes that must be suppressed by the input filter	t_{SP}	N/A	N/A	0	50	ns

1. The maximum SCL Clock Frequency in Fast mode with maximum bus loading can only be achieved when using the High drive pins across the full voltage range and when using the Normal drive pins and VDD ≥ 2.7 V.
2. The master mode I²C deasserts ACK of an address byte simultaneously with the falling edge of SCL. If no slaves acknowledge this address byte, then a negative hold time can result, depending on the edge rates of the SDA and SCL lines.
3. The maximum tHD; DAT must be met only if the device does not stretch the LOW period (tLOW) of the SCL signal.
4. Input signal Slew = 10 ns and Output Load = 50 pF
5. Set-up time in slave-transmitter mode is 1 IPBus clock period, if the TX FIFO is empty.
6. A Fast mode I²C bus device can be used in a Standard mode I2C bus system, but the requirement $t_{SU; DAT} \geq 250$ ns must then be met. This is automatically the case if the device does not stretch the LOW period of the SCL signal. If such a device does stretch the LOW period of the SCL signal, then it must output the next data bit to the SDA line $t_{rmax} + t_{SU; DAT} = 1000 + 250 = 1250$ ns (according to the Standard mode I²C bus specification) before the SCL line is released.
7. C_b = total capacitance of the one bus line in pF.

Table 40. I²C 1 Mbps timing

Characteristic	Symbol	Minimum	Maximum	Unit
SCL Clock Frequency	f_{SCL}	0	1[1]	MHz
Hold time (repeated) START condition. After this period, the first clock pulse is generated.	t_{HD}; STA	0.26	—	µs
LOW period of the SCL clock	t_{LOW}	0.5	—	µs
HIGH period of the SCL clock	t_{HIGH}	0.26	—	µs
Set-up time for a repeated START condition	t_{SU}; STA	0.26	—	µs
Data hold time for I_2C bus devices	t_{HD}; DAT	0	—	µs
Data set-up time	t_{SU}; DAT	50	—	ns
Rise time of SDA and SCL signals	t_r	20 +0.1C_b, [2]	120	ns
Fall time of SDA and SCL signals	t_f	20 +0.1C_b[2]	120	ns
Set-up time for STOP condition	t_{SU}; STO	0.26	—	µs
Bus free time between STOP and START condition	t_{BUF}	0.5	—	µs
Pulse width of spikes that must be suppressed by the input filter	t_{SP}	0	50	ns

1. The maximum SCL clock frequency of 1 Mbps can support maximum bus loading when using the High drive pins across the full voltage range.
2. C_b = total capacitance of the one bus line in pF.

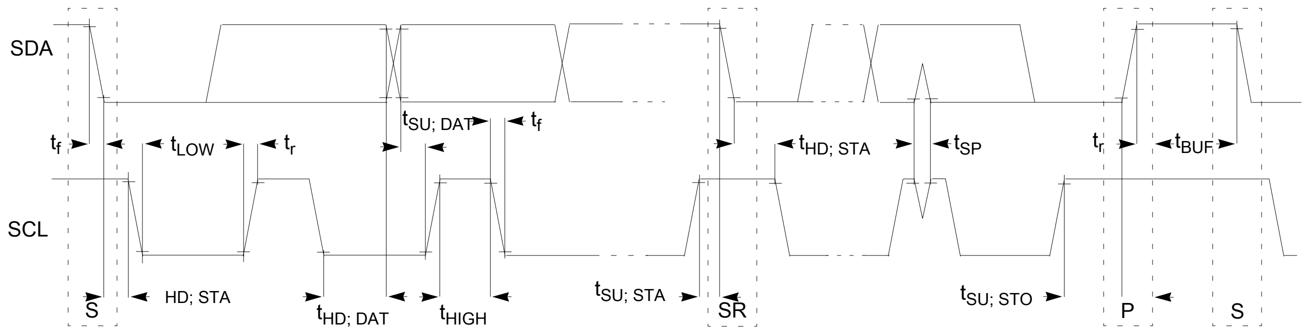


Figure 23. Timing definition for devices on the I²C bus

3.8.5 UART switching specifications

See General switching specifications.

3.8.6 I2S/SAI switching specifications

This section provides the AC timing for the I2S/SAI module in master mode (clocks are driven) and slave mode (clocks are input). All timing is given for noninverted serial clock polarity (TCR2[BCP] is 0, RCR2[BCP] is 0) and a noninverted frame sync (TCR4[FSP] is 0, RCR4[FSP] is 0). If the polarity of the clock and/or the frame sync have been inverted, all the timing remains valid by inverting the bit clock signal (BCLK) and/or the frame sync (FS) signal shown in the following figures.

3.8.6.1 Normal Run, Wait and Stop mode performance over a limited operating voltage range

This section provides the operating performance over a limited operating voltage for the device in Normal Run, Wait and Stop modes.

Table 41. I2S/SAI master mode timing in Normal Run, Wait and Stop modes (limited voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
S1	I2S_MCLK cycle time	40	—	ns
S2	I2S_MCLK pulse width high/low	45%	55%	MCLK period
S3	I2S_TX_BCLK/I2S_RX_BCLK cycle time (output)	80	—	ns
S4	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low	45%	55%	BCLK period

Table continues on the next page...

Table 41. I2S/SAI master mode timing in Normal Run, Wait and Stop modes (limited voltage range) (continued)

Num.	Characteristic	Min.	Max.	Unit
S5	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output valid	—	15	ns
S6	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output invalid	0	—	ns
S7	I2S_TX_BCLK to I2S_TXD valid	—	15	ns
S8	I2S_TX_BCLK to I2S_TXD invalid	0	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK	18	—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns

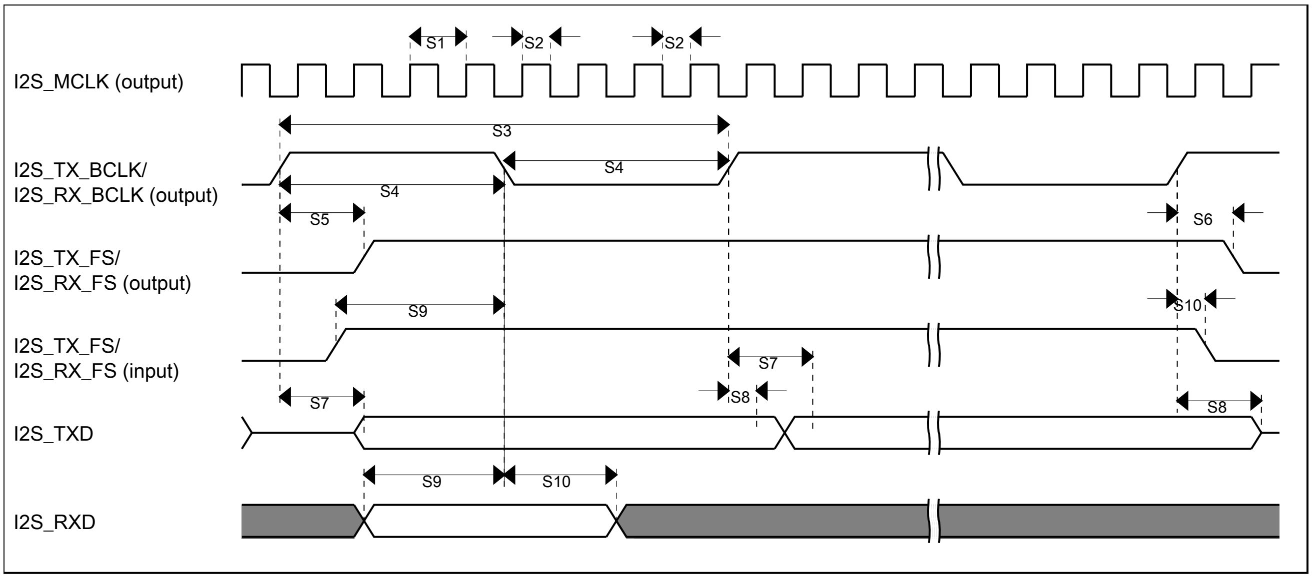


Figure 24. I2S/SAI timing — master modes

Table 42. I2S/SAI slave mode timing in Normal Run, Wait and Stop modes (limited voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
S11	I2S_TX_BCLK/I2S_RX_BCLK cycle time (input)	80	—	ns
S12	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_TX_FS/I2S_RX_FS input setup before I2S_TX_BCLK/I2S_RX_BCLK	4.5	—	ns
S14	I2S_TX_FS/I2S_RX_FS input hold after I2S_TX_BCLK/I2S_RX_BCLK	2	—	ns

Table continues on the next page...

Table 42. I2S/SAI slave mode timing in Normal Run, Wait and Stop modes (limited voltage range) (continued)

Num.	Characteristic	Min.	Max.	Unit
S15	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output valid	—	20	ns
S16	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_RX_BCLK	4.5	—	ns
S18	I2S_RXD hold after I2S_RX_BCLK	2	—	ns
S19	I2S_TX_FS input assertion to I2S_TXD output valid[1]	—	25	ns

1. Applies to first bit in each frame and only if the TCR4[FSE] bit is clear

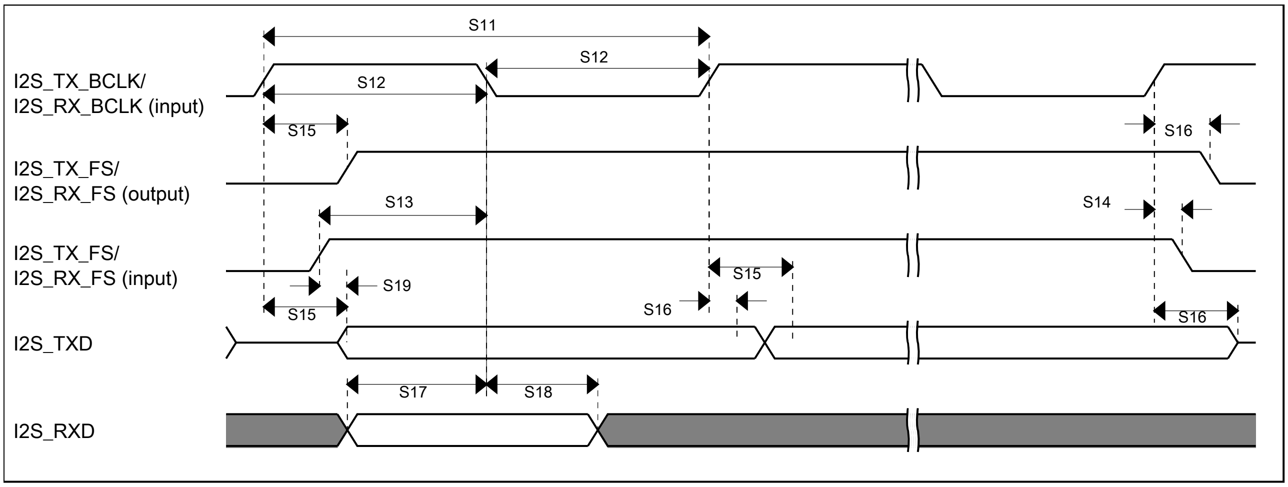


Figure 25. I2S/SAI timing — slave modes

3.8.6.2 Normal Run, Wait and Stop mode performance over the full operating voltage range

This section provides the operating performance over the full operating voltage for the device in Normal Run, Wait and Stop modes.

Table 43. I2S/SAI master mode timing in Normal Run, Wait and Stop modes (full voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	I2S_MCLK cycle time	40	—	ns
S2	I2S_MCLK pulse width high/low	45%	55%	MCLK period
S3	I2S_TX_BCLK/I2S_RX_BCLK cycle time (output)	80	—	ns
S4	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low	45%	55%	BCLK period

Table continues on the next page...

Table 43. I2S/SAI master mode timing in Normal Run, Wait and Stop modes (full voltage range) (continued)

Num.	Characteristic	Min.	Max.	Unit
S5	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output valid	—	15	ns
S6	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output invalid	-1.0	—	ns
S7	I2S_TX_BCLK to I2S_TXD valid	—	15	ns
S8	I2S_TX_BCLK to I2S_TXD invalid	0	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK	27	—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns

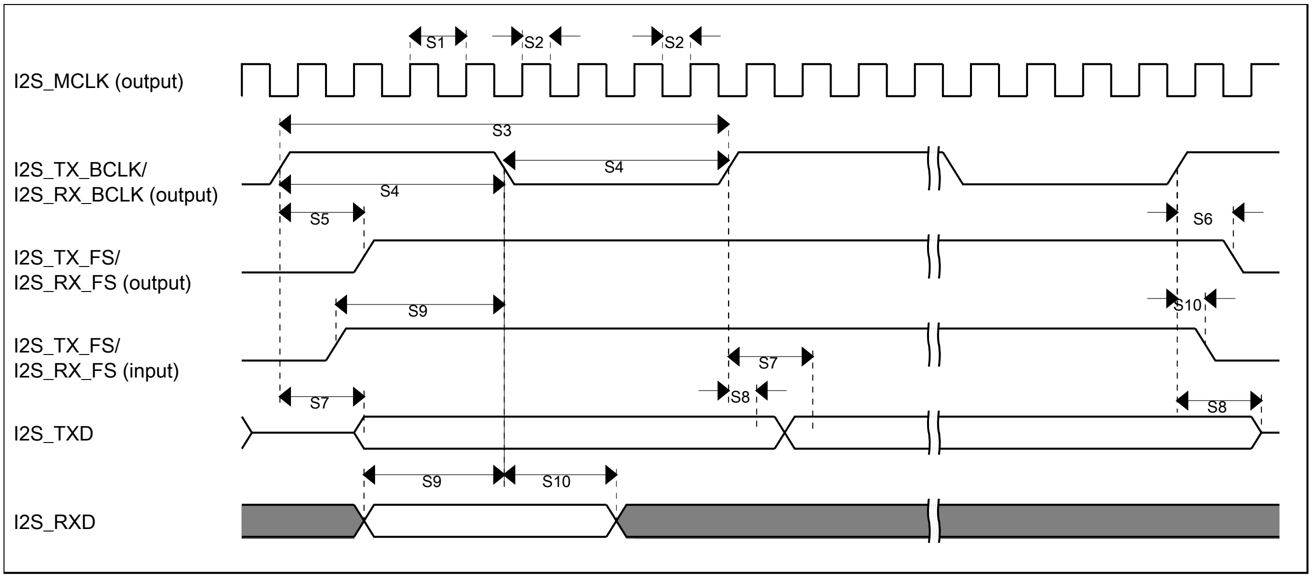


Figure 26. I2S/SAI timing — master modes

Table 44. I2S/SAI slave mode timing in Normal Run, Wait and Stop modes (full voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S11	I2S_TX_BCLK/I2S_RX_BCLK cycle time (input)	80	—	ns
S12	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_TX_FS/I2S_RX_FS input setup before I2S_TX_BCLK/I2S_RX_BCLK	5.8	—	ns
S14	I2S_TX_FS/I2S_RX_FS input hold after I2S_TX_BCLK/I2S_RX_BCLK	2	—	ns

Table continues on the next page...

Table 44. I2S/SAI slave mode timing in Normal Run, Wait and Stop modes (full voltage range) (continued)

Num.	Characteristic	Min.	Max.	Unit
S15	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output valid	—	28.5	ns
S16	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_RX_BCLK	5.8	—	ns
S18	I2S_RXD hold after I2S_RX_BCLK	2	—	ns
S19	I2S_TX_FS input assertion to I2S_TXD output valid[1]	—	26.3	ns

1. Applies to first bit in each frame and only if the TCR4[FSE] bit is clear

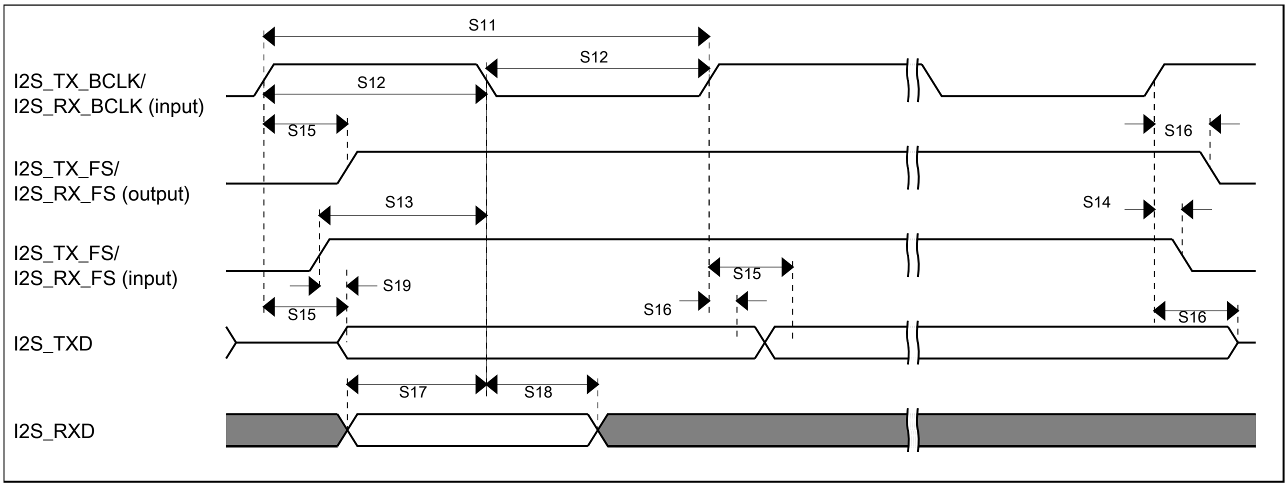


Figure 27. I2S/SAI timing — slave modes

3.8.6.3 VLPR, VLPW, and VLPS mode performance over the full operating voltage range

This section provides the operating performance over the full operating voltage for the device in VLPR, VLPW, and VLPS modes.

Table 45. I2S/SAI master mode timing in VLPR, VLPW, and VLPS modes (full voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	I2S_MCLK cycle time	62.5	—	ns
S2	I2S_MCLK pulse width high/low	45%	55%	MCLK period
S3	I2S_TX_BCLK/I2S_RX_BCLK cycle time (output)	250	—	ns
S4	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low	45%	55%	BCLK period

Table continues on the next page...

Table 45. I2S/SAI master mode timing in VLPR, VLPW, and VLPS modes (full voltage range) (continued)

Num.	Characteristic	Min.	Max.	Unit
S5	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output valid	—	45	ns
S6	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output invalid	-1	—	ns
S7	I2S_TX_BCLK to I2S_TXD valid	—	45	ns
S8	I2S_TX_BCLK to I2S_TXD invalid	0	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK	45	—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns

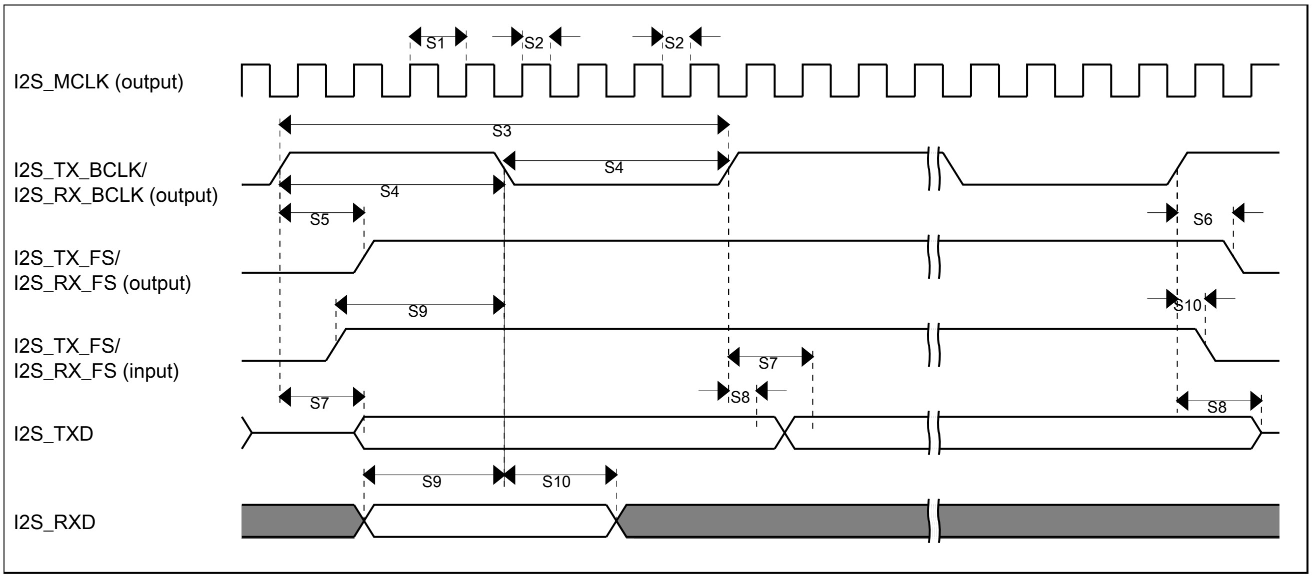


Figure 28. I2S/SAI timing — master modes

Table 46. I2S/SAI slave mode timing in VLPR, VLPW, and VLPS modes (full voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S11	I2S_TX_BCLK/I2S_RX_BCLK cycle time (input)	250	—	ns
S12	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_TX_FS/I2S_RX_FS input setup before I2S_TX_BCLK/I2S_RX_BCLK	30	—	ns
S14	I2S_TX_FS/I2S_RX_FS input hold after I2S_TX_BCLK/I2S_RX_BCLK	7	—	ns

Table continues on the next page...

Table 46. I2S/SAI slave mode timing in VLPR, VLPW, and VLPS modes (full voltage range) (continued)

Num.	Characteristic	Min.	Max.	Unit
S15	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output valid	—	63	ns
S16	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_RX_BCLK	30	—	ns
S18	I2S_RXD hold after I2S_RX_BCLK	4	—	ns
S19	I2S_TX_FS input assertion to I2S_TXD output valid[1]	—	72	ns

1. Applies to first bit in each frame and only if the TCR4[FSE] bit is clear

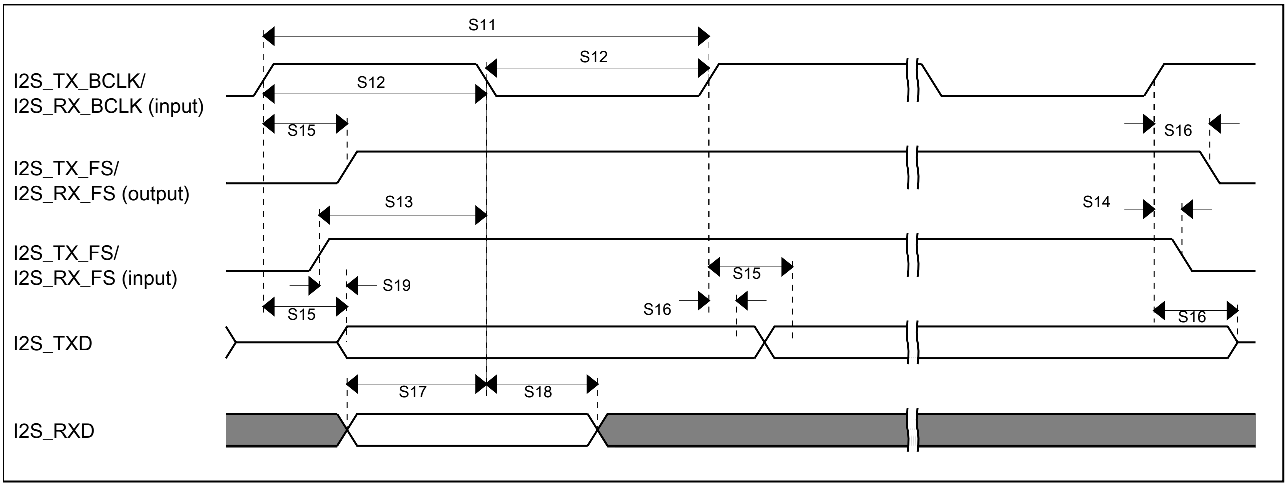


Figure 29. I2S/SAI timing — slave modes

4 Dimensions

4.1 Obtaining package dimensions

Package dimensions are provided in package drawings.

To find a package drawing, go to freescale.com and perform a keyword search for the drawing's document number:

If you want the drawing for this package	Then use this document number
49-pin WLCSP	98ASA00718D

5 Pinout

5.1 K22 Signal Multiplexing and Pin Assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Control Module is responsible for selecting which ALT functionality is available on each pin.

NOTE

This package offering is subject to removal.

49 WLC SP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
B6	PTE0/ CLKOUT32K	ADC1_SE4a	ADC1_SE4a	PTE0/ CLKOUT32K	SPI1_PCS1	UART1_TX			I2C1_SDA	RTC_ CLKOUT	
D5	PTE1/ LLWU_P0	ADC1_SE5a	ADC1_SE5a	PTE1/ LLWU_P0	SPI1_SOUT	UART1_RX			I2C1_SCL	SPI1_SIN	
E5	PTE2/ LLWU_P1	ADC1_SE6a	ADC1_SE6a	PTE2/ LLWU_P1	SPI1_SCK	UART1_CTS_ b					
A7	PTE3	ADC1_SE7a	ADC1_SE7a	PTE3	SPI1_SIN	UART1_RTS_ b				SPI1_SOUT	
E4	PTE4/ LLWU_P2	DISABLED		PTE4/ LLWU_P2	SPI1_PCS0	LPUART0_TX					
D4	PTE5	DISABLED		PTE5	SPI1_PCS2	LPUART0_RX					
B7	VDD	VDD	VDD								
C6	VSS	VSS	VSS								
C6	VSS	VSS	VSS								
C7	USB0_DP	USB0_DP	USB0_DP								
D7	USB0_DM	USB0_DM	USB0_DM								
D6	USBVDD	USBVDD	USBVDD								
F7	VDDA	VDDA	VDDA								
F7	VREFH	VREFH	VREFH								
G7	VREFL	VREFL	VREFL								
G7	VSSA	VSSA	VSSA								
G6	VREF_OUT/ CMP1_IN5/ CMP0_IN5/ ADC1_SE18	VREF_OUT/ CMP1_IN5/ CMP0_IN5/ ADC1_SE18	VREF_OUT/ CMP1_IN5/ CMP0_IN5/ ADC1_SE18								
F5	XTAL32	XTAL32	XTAL32								
G5	EXTAL32	EXTAL32	EXTAL32								
G4	VBAT	VBAT	VBAT								

49 WLCSP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
F4	PTA0	JTAG_TCLK/ SWD_CLK/ EZP_CLK		PTA0	UART0_CTS_ b	FTM0_CH5				JTAG_TCLK/ SWD_CLK	EZP_CLK
F6	PTA1	JTAG_TDI/ EZP_DI		PTA1	UART0_RX	FTM0_CH6				JTAG_TDI	EZP_DI
E7	PTA2	JTAG_TDO/ TRACE_ SWO/ EZP_DO		PTA2	UART0_TX	FTM0_CH7				JTAG_TDO/ TRACE_SWO	EZP_DO
E6	PTA3	JTAG_TMS/ SWD_DIO		PTA3	UART0_RTS_ b	FTM0_CH0				JTAG_TMS/ SWD_DIO	
F3	PTA4/ LLWU_P3	NMI_b/ EZP_CS_b		PTA4/ LLWU_P3		FTM0_CH1				NMI_b	EZP_CS_b
G3	VDD	VDD	VDD								
F2	VSS	VSS	VSS								
G2	PTA18	EXTAL0	EXTAL0	PTA18		FTM0_FLT2	FTM_CLKIN0				
G1	PTA19	XTAL0	XTAL0	PTA19		FTM1_FLT0	FTM_CLKIN1		LPTMR0_ ALT1		
F1	RESET_b	RESET_b	RESET_b								
E3	PTB0/ LLWU_P5	ADC0_SE8/ ADC1_SE8	ADC0_SE8/ ADC1_SE8	PTB0/ LLWU_P5	I2C0_SCL	FTM1_CH0			FTM1_QD_ PHA		
E2	PTB1	ADC0_SE9/ ADC1_SE9	ADC0_SE9/ ADC1_SE9	PTB1	I2C0_SDA	FTM1_CH1			FTM1_QD_ PHB		
D2	PTB2	ADC0_SE12	ADC0_SE12	PTB2	I2C0_SCL	UART0_RTS_ b			FTM0_FLT3		
E1	PTB3	ADC0_SE13	ADC0_SE13	PTB3	I2C0_SDA	UART0_CTS_ b			FTM0_FLT0		
D1	PTB16	DISABLED		PTB16	SPI1_SOUT	UART0_RX	FTM_CLKIN0		EWM_IN		
C2	PTB17	DISABLED		PTB17	SPI1_SIN	UART0_TX	FTM_CLKIN1		EWM_OUT_b		
C1	PTC0	ADC0_SE14	ADC0_SE14	PTC0	SPI0_PCS4	PDB0_ EXTRG	USB_SOF_ OUT				
B1	PTC1/ LLWU_P6	ADC0_SE15	ADC0_SE15	PTC1/ LLWU_P6	SPI0_PCS3	UART1_RTS_ b	FTM0_CH0		I2S0_TXD0	LPUART0_ RTS_b	
B2	PTC2	ADC0_SE4b/ CMP1_IN0	ADC0_SE4b/ CMP1_IN0	PTC2	SPI0_PCS2	UART1_CTS_ b	FTM0_CH1		I2S0_TX_FS	LPUART0_ CTS_b	
A1	PTC3/ LLWU_P7	CMP1_IN1	CMP1_IN1	PTC3/ LLWU_P7	SPI0_PCS1	UART1_RX	FTM0_CH2	CLKOUT	I2S0_TX_ BCLK	LPUART0_RX	
C6	VSS	VSS	VSS								
B7	VDD	VDD	VDD								
A2	PTC4/ LLWU_P8	DISABLED		PTC4/ LLWU_P8	SPI0_PCS0	UART1_TX	FTM0_CH3		CMP1_OUT	LPUART0_TX	
D3	PTC5/ LLWU_P9	DISABLED		PTC5/ LLWU_P9	SPI0_SCK	LPTMR0_ ALT2	I2S0_RXD0		CMP0_OUT	FTM0_CH2	
C3	PTC6/ LLWU_P10	CMP0_IN0	CMP0_IN0	PTC6/ LLWU_P10	SPI0_SOUT	PDB0_ EXTRG	I2S0_RX_ BCLK		I2S0_MCLK		

49 WLCSP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
B3	PTC7	CMP0_IN1	CMP0_IN1	PTC7	SPI0_SIN	USB_SOF_OUT	I2S0_RX_FS				
A3	PTD0/LLWU_P12	DISABLED		PTD0/LLWU_P12	SPI0_PCS0	UART2_RTS_b			LPUART0_RTS_b		
A4	PTD1	ADC0_SE5b	ADC0_SE5b	PTD1	SPI0_SCK	UART2_CTS_b			LPUART0_CTS_b		
B4	PTD2/LLWU_P13	DISABLED		PTD2/LLWU_P13	SPI0_SOUT	UART2_RX			LPUART0_RX	I2C0_SCL	
C4	PTD3	DISABLED		PTD3	SPI0_SIN	UART2_TX			LPUART0_TX	I2C0_SDA	
A5	PTD4/LLWU_P14	DISABLED		PTD4/LLWU_P14	SPI0_PCS1	UART0_RTS_b	FTM0_CH4		EWM_IN	SPI1_PCS0	
B5	PTD5	ADC0_SE6b	ADC0_SE6b	PTD5	SPI0_PCS2	UART0_CTS_b	FTM0_CH5		EWM_OUT_b	SPI1_SCK	
C5	PTD6/LLWU_P15	ADC0_SE7b	ADC0_SE7b	PTD6/LLWU_P15	SPI0_PCS3	UART0_RX	FTM0_CH6		FTM0_FLT0	SPI1_SOUT	
A6	PTD7	DISABLED		PTD7		UART0_TX	FTM0_CH7		FTM0_FLT1	SPI1_SIN	

5.2 K22 Pinouts

This figure shows the pinout diagram for the devices supported by this document. Many signals may be multiplexed onto a single pin. To determine what signals can be used on which pin, see the previous section.

NOTE

This package offering is subject to removal.

	1	2	3	4	5	6	7	
A	PTC3/ LLWU_P7	PTC4/ LLWU_P8	PTD0/ LLWU_P12	PTD1	PTD4/ LLWU_P14	PTD7	PTE3	A
B	PTC1/ LLWU_P6	PTC2	PTC7	PTD2/ LLWU_P13	PTD5	PTE0/ CLKOUT32K	VDD	B
C	PTC0	PTB17	PTC6/ LLWU_P10	PTD3	PTD6/ LLWU_P15	VSS	USB0_DP	C
D	PTB16	PTB2	PTC5/ LLWU_P9	PTE5	PTE1/ LLWU_P0	USBVDD	USB0_DM	D
E	PTB3	PTB1	PTB0/ LLWU_P5	PTE4/ LLWU_P2	PTE2/ LLWU_P1	PTA3	PTA2	E
F	RESET_b	VSS	PTA4/ LLWU_P3	PTA0	XTAL32	PTA1	VDDA/ VREFH	F
G	PTA19	PTA18	VDD	VBAT	EXTAL32	VREF_OUT/ CMP1_IN5/ CMP0_IN5/ ADC1_SE18	VSSA/ VREFL	G

Figure 30. K22 49 WLCSP Pinout Diagram

6 Part identification

6.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

6.2 Format

Part numbers for this device have the following format:

Q K## A M FFF R T PP CC N

6.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values
Q	Qualification status	• M = Fully qualified, general market flow, full reel • P = Prequalification • K = Fully qualified, general market flow, 100 piece reel
K##	Kinetis family	• K22
A	Key attribute	• D = Cortex-M4 w/ DSP • F = Cortex-M4 w/ DSP and FPU
M	Flash memory type	• N = Program flash only • X = Program flash and FlexMemory
FFF	Program flash memory size	• 128 = 128 KB • 256 = 256 KB • 512 = 512 KB
R	Silicon revision	• Z = Initial • (Blank) = Main • A = Revision after main
T	Temperature range (°C)	• V = –40 to 105 • C = –40 to 85
PP	Package identifier	• AK = 49 WLCSP (2.915 mm x 3.142 mm)
CC	Maximum CPU frequency (MHz)	• 5 = 50 MHz • 7 = 72 MHz • 10 = 100 MHz • 12 = 120 MHz • 15 = 150 MHz
N	Packaging type	• R = Tape and reel

6.4 Example

This is an example part number:

MK22FN128VDC10

6.5 49-pin WLCSP part marking

The 49-pin WLCSP package parts follow the part-marking scheme in the following table.

Table 47. 49-pin WLCSP part marking

MK Part number	MK Part Marking
MK22FN128CAK10R	MK22FN128CAK10

7 Revision History

The following table provides a revision history for this document.

Table 48. Revision History

Rev. No.	Date	Substantial Changes
5	4/2015	Initial public release

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